



MACRONIX
INTERNATIONAL Co., LTD.

MX29LV320E T/B

MX29LV320E T/B

DATASHEET

Contents

| | |
|--|-----------|
| FEATURES | 5 |
| GENERAL DESCRIPTION | 6 |
| PIN CONFIGURATION | 7 |
| PIN DESCRIPTION | 8 |
| BLOCK DIAGRAM | 9 |
| BLOCK DIAGRAM DESCRIPTION | 10 |
| BLOCK STRUCTURE | 11 |
| Table 1.a: MX29LV320ET SECTOR GROUP ARCHITECTURE..... | 11 |
| Table 1.b: MX29LV320EB SECTOR GROUP ARCHITECTURE | 13 |
| BUS OPERATION | 15 |
| Table 2-1. BUS OPERATION | 15 |
| Table 2-2. BUS OPERATION | 16 |
| FUNCTIONAL OPERATION DESCRIPTION | 17 |
| READ OPERATION | 17 |
| WRITE OPERATION..... | 17 |
| DEVICE RESET | 17 |
| STANDBY MODE..... | 17 |
| OUTPUT DISABLE | 17 |
| BYTE/WORD SELECTION | 18 |
| HARDWARE WRITE PROTECT..... | 18 |
| ACCELERATED PROGRAMMING OPERATION | 18 |
| TEMPORARY SECTOR GROUP UNPROTECT OPERATION | 18 |
| SECTOR GROUP PROTECT OPERATION | 18 |
| CHIP UNPROTECT OPERATION..... | 19 |
| AUTOMATIC SELECT BUS OPERATIONS..... | 19 |
| SECTOR LOCK STATUS VERIFICATION | 19 |
| READ SILICON ID MANUFACTURER CODE..... | 19 |
| READ SILICON ID MX29LV320ET CODE..... | 19 |
| READ SILICON ID MX29LV320EB CODE..... | 19 |
| READ INDICATOR BIT (Q7) FOR SECURITY SECTOR | 20 |
| INHERENT DATA PROTECTION..... | 20 |
| COMMAND COMPLETION..... | 20 |
| LOW VCC WRITE INHIBIT | 20 |
| WRITE PULSE "GLITCH" PROTECTION..... | 20 |
| LOGICAL INHIBIT | 20 |
| POWER-UP SEQUENCE | 20 |
| POWER-UP WRITE INHIBIT | 21 |
| POWER SUPPLY DECOUPLING | 21 |

| | |
|---|-----------|
| COMMAND OPERATIONS | 22 |
| TABLE 3. MX29LV320E T/B COMMAND DEFINITIONS | 22 |
| AUTOMATIC PROGRAMMING OF THE MEMORY ARRAY | 23 |
| SECTOR ERASE | 24 |
| CHIP ERASE..... | 25 |
| SECTOR ERASE SUSPEND..... | 25 |
| SECTOR ERASE RESUME..... | 26 |
| AUTOMATIC SELECT OPERATIONS | 26 |
| AUTOMATIC SELECT COMMAND SEQUENCE | 26 |
| READ MANUFACTURER ID OR DEVICE ID | 27 |
| SECURITY SECTOR LOCK STATUS..... | 27 |
| VERIFY SECTOR GROUP PROTECTION..... | 27 |
| SECURITY SECTOR FLASH MEMORY REGION | 27 |
| FACTORY LOCKED: SECURITY SECTOR PROGRAMMED AND PROTECTED AT THE FACTORY | 27 |
| CUSTOMER LOCKABLE: SECURITY SECTOR NOT PROGRAMMED OR PROTECTED AT THE FACTORY..... | 28 |
| ENTER AND EXIT SECURITY SECTOR..... | 28 |
| RESET OPERATION | 29 |
| COMMON FLASH MEMORY INTERFACE (CFI) MODE | 30 |
| QUERY COMMAND AND COMMAND FLASH MEMORY INTERFACE (CFI) MODE | 30 |
| Table 4-1. CFI mode: Identification Data Values | 30 |
| Table 4-2. CFI Mode: System Interface Data Values | 30 |
| Table 4-3. CFI Mode: Device Geometry Data Values..... | 31 |
| Table 4-4. CFI Mode: Primary Vendor-Specific Extended Query Data Values..... | 32 |
| ELECTRICAL CHARACTERISTICS | 33 |
| ABSOLUTE MAXIMUM STRESS RATINGS..... | 33 |
| OPERATING TEMPERATURE AND VOLTAGE..... | 33 |
| DC CHARACTERISTICS | 34 |
| SWITCHING TEST CIRCUIT | 35 |
| SWITCHING TEST WAVEFORM..... | 35 |
| AC CHARACTERISTICS | 36 |
| WRITE COMMAND OPERATION | 37 |
| Figure 1. COMMAND WRITE OPERATION..... | 37 |
| READ/RESET OPERATION | 38 |
| Figure 2. READ TIMING WAVEFORM..... | 38 |
| Figure 3. RESET# TIMING WAVEFORM..... | 39 |
| ERASE/PROGRAM OPERATION | 40 |
| Figure 4. AUTOMATIC CHIP ERASE TIMING WAVEFORM | 40 |
| Figure 5. AUTOMATIC CHIP ERASE ALGORITHM FLOWCHART | 41 |
| Figure 6. AUTOMATIC SECTOR ERASE TIMING WAVEFORM | 42 |
| Figure 7. AUTOMATIC SECTOR ERASE ALGORITHM FLOWCHART | 43 |
| Figure 8. ERASE SUSPEND/RESUME FLOWCHART | 44 |



| | |
|--|-----------|
| Figure 9. AUTOMATIC PROGRAM TIMING WAVEFORM..... | 45 |
| Figure 10. ACCELERATED PROGRAM TIMING DIAGRAM | 45 |
| Figure 11. CE# CONTROLLED WRITE TIMING WAVEFORM..... | 46 |
| Figure 12. AUTOMATIC PROGRAMMING ALGORITHM FLOWCHART..... | 47 |
| SECTOR GROUP PROTECT/CHIP UNPROTECT | 48 |
| Figure 13. SECTOR GROUP PROTECT/CHIP UNPROTECT WAVEFORM (RESET# Control) | 48 |
| Figure 14. IN-SYSTEM SECTOR GROUP PROTECT WITH RESET#=Vhv..... | 49 |
| Figure 15. CHIP UNPROTECT ALGORITHM WITH RESET#=Vhv..... | 50 |
| Table 5. TEMPORARY SECTOR GROUP UNPROTECT..... | 51 |
| Figure 16. TEMPORARY SECTOR GROUP UNPROTECT WAVEFORM | 51 |
| Figure 17. TEMPORARY SECTOR GROUP UNPROTECT FLOWCHART | 52 |
| Figure 18. SILICON ID READ TIMING WAVEFORM..... | 53 |
| WRITE OPERATION STATUS..... | 54 |
| Figure 19. DATA# POLLING TIMING WAVEFORM (DURING AUTOMATIC ALGORITHM)..... | 54 |
| Figure 20. DATA# POLLING ALGORITHM | 55 |
| Figure 21. TOGGLE BIT TIMING WAVEFORM (DURING AUTOMATIC ALGORITHM)..... | 56 |
| Figure 22. TOGGLE BIT ALGORITHM..... | 57 |
| Figure 23. BYTE# TIMING WAVEFORM FOR READ OPERATIONS (BYTE# switching from byte mode to word mode) | 58 |
| RECOMMENDED OPERATING CONDITIONS..... | 59 |
| ERASE AND PROGRAMMING PERFORMANCE | 60 |
| DATA RETENTION | 60 |
| LATCH-UP CHARACTERISTICS | 60 |
| TSOP PIN CAPACITANCE | 60 |
| ORDERING INFORMATION | 61 |
| PART NAME DESCRIPTION | 62 |
| PACKAGE INFORMATION..... | 63 |
| REVISION HISTORY | 67 |

32M-BIT [4M x 8 / 2M x 16] 3V SUPPLY FLASH MEMORY

FEATURES

GENERAL FEATURES

- Byte/Word switchable
 - 4,194,304 x 8 / 2,097,152 x 16
- Sector Structure
 - 8K-Byte x 8 and 64K-Byte x 63
- Extra 256-Byte sector for security
 - Features factory locked and identifiable, and customer lockable
- Twenty-Four Sector Groups
 - Provides sector group protect function to prevent program or erase operation in the protected sector group
 - Provides chip unprotect function to allow code changing
 - Provides temporary sector group unprotect function for code changing in previously protected sector groups
- Power Supply Operation
 - Vcc 2.7 to 3.6 volt for read, erase, and program operations
- Latch-up protected to 100mA from -1V to 1.5 x Vcc
- Low Vcc write inhibit : Vcc ≤ V_{Iko}
- Compatible with JEDEC standard
 - Pinout and software compatible to single power supply Flash
- **Functional compatible with MX29LV320D T/B device**

PERFORMANCE

- High Performance
 - Fast access time: 70ns
 - Fast program time: 11us/word typical utilizing accelerate function
 - Fast erase time: 0.7s/sector, 35s/chip (typical)
- Low Power Consumption
 - Low active read current: 10mA (typical) at 5MHz
 - Low standby current: 5uA (typical)
- Typical 100,000 erase/program cycle
- 20 years data retention

SOFTWARE FEATURES

- Erase Suspend/ Erase Resume
 - Suspends sector erase operation to read data from or program data to another sector which is not being erased
- Status Reply
 - Data# Polling & Toggle bits provide detection of program and erase operation completion
- Support Common Flash Interface (CFI)

HARDWARE FEATURES

- Ready/Busy# (RY/BY#) Output
 - Provides a hardware method of detecting program and erase operation completion
- Hardware Reset (RESET#) Input
 - Provides a hardware method to reset the internal state machine to read mode
- WP#/ACC input pin
 - Provides accelerated program capability

PACKAGE

- 44-Pin SOP
- 48-Pin TSOP
- 48-Ball TFBGA (6 x 8mm)
- 48-Ball LFBGA (6 x 8mm)
- **All devices are RoHS Compliant**

GENERAL DESCRIPTION

MX29LV320E T/B is a 32Mbit flash memory that can be organized as 4Mbytes of 8 bits each or 2Mbytes of 16 bits each. These devices operate over a voltage range of 2.7V to 3.6V typically using a 3V power supply input. The memory array is divided into 64 equal 64 Kilo byte blocks. However, depending on the device being used as a Top-Boot or Bottom-Boot device, the top or the bottom first block is further subdivided into 8 equal 8Kbyte blocks. The outermost two sectors at the top or at the bottom can be protected at the boot blocks for this device. This flash memory also provides an additional factory lockable or customer lockable 256byte sector to provide security feature.

The MX29LV320E T/B is offered in a 44-pin SOP, a 48-pin TSOP and a 48-ball BGA(TFBGA/LFBGA) JEDEC standard package. These packages are offered in leaded, as well as lead-free versions that are compliant to the RoHS specifications. The software algorithm used for this device also adheres to the JEDEC standard for single power supply devices. These flash parts can be programmed in system or on commercially available EPROM/Flash programmers.

Separate OE# and CE# (Output Enable and Chip Enable) signals are provided to simplify system design. When used with high speed processors, the 70ns read access time of this flash memory permits operation with minimal time lost due to system timing delays.

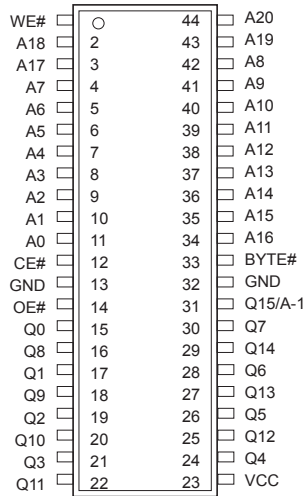
The automatic erase algorithm provided on Macronix flash memories perform an automatic program prior to program. The user only needs to provide a write command to the command register. The on-chip state machine automatically controls the program and erase functions including all necessary internal timings. Since erase operations take much longer time than read operations, erase can be interrupted to perform read operations in other sectors of the device. For this, Erase Suspend operation along with erase resume operation are provided. Data# polling or toggle bits are used to indicate the end of the erase/program operation.

These devices are manufactured at the Macronix fabrication facility using the time tested and proven Macronix's advanced technology. This proprietary non-epi process provides a very high degree of latch-up protection for stresses up to 100 milliamperes on address and data pins from -1V to 1.5xVCC.

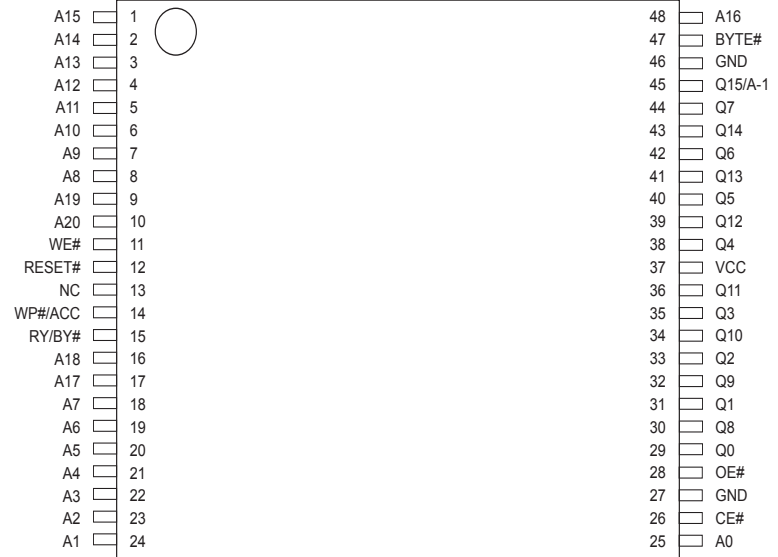
With low power consumption and enhanced hardware and software features, this flash memory retains data reliably for at least twenty years. Erase and programming functions have been tested to meet a typical specification of 100,000 cycles of operation.

PIN CONFIGURATION

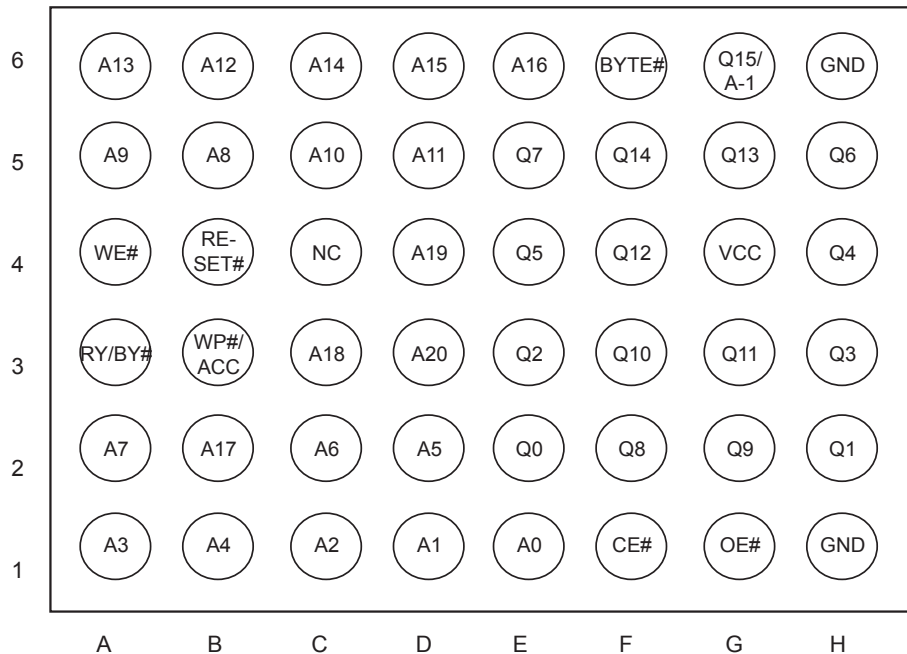
44 SOP



48 TSOP



48-Ball TFBGA/LFBGA (6mm x 8mm, Top View, Balls Facing Down)

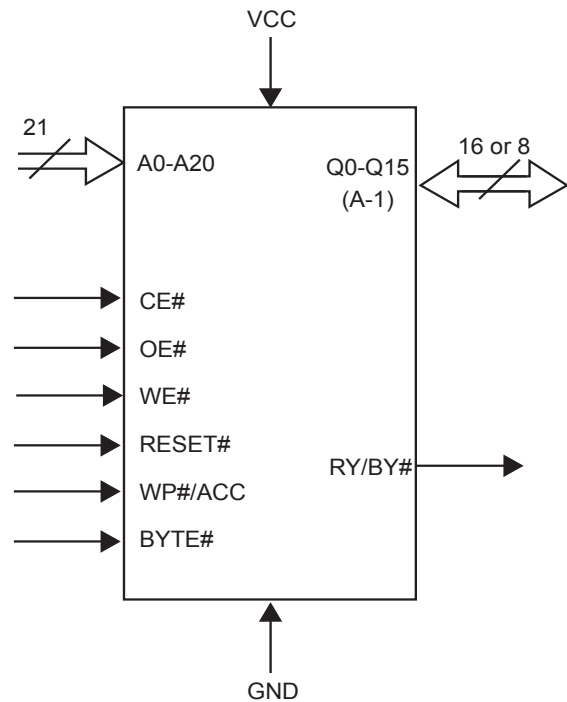


PIN DESCRIPTION

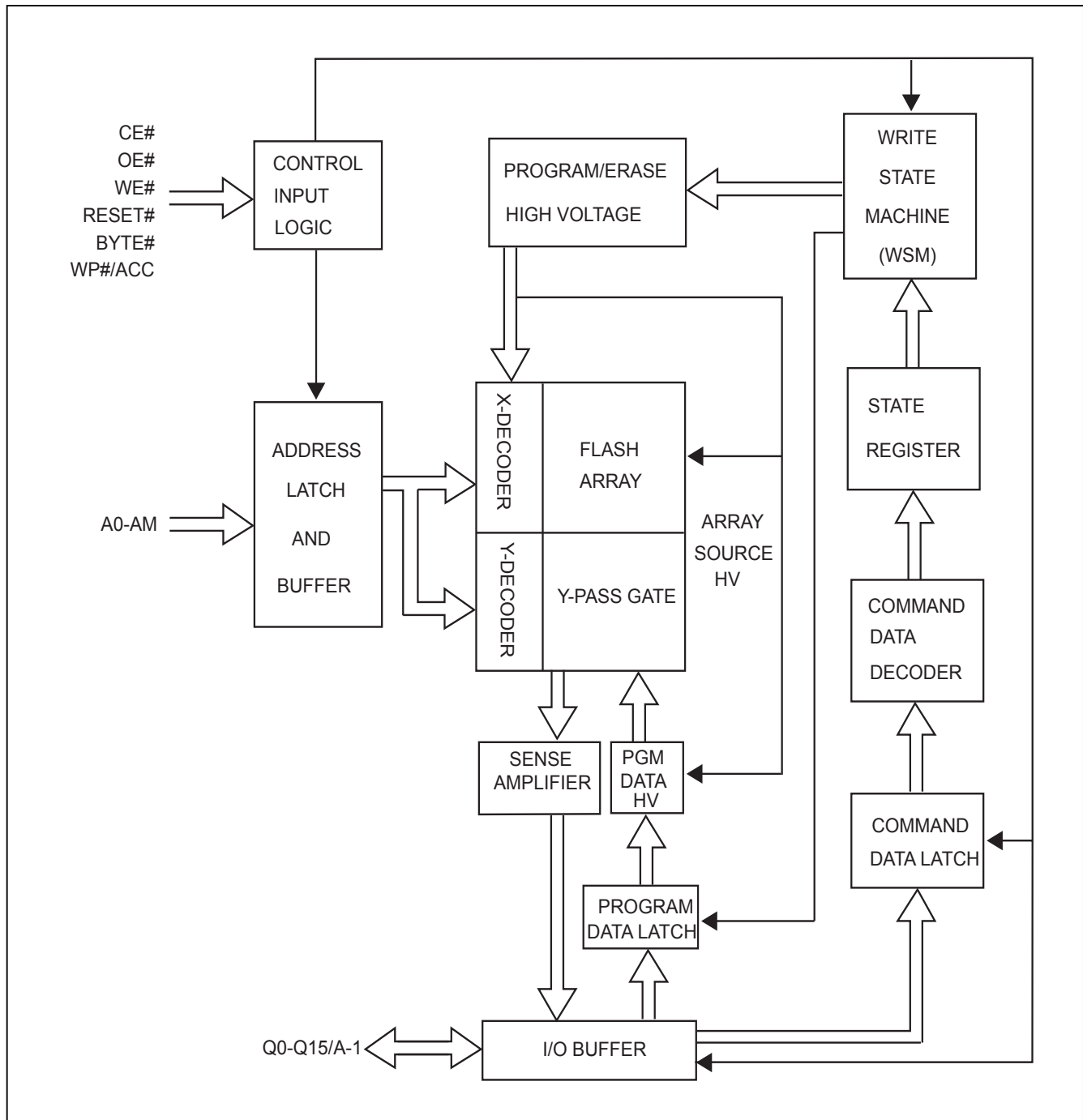
| SYMBOL | PIN NAME |
|---------|---|
| A0~A20 | Address Input |
| Q0~Q14 | 15 Data Inputs/Outputs |
| Q15/A-1 | Q15(Data Input/Output, word mode); A-1(LSB Address Input, byte mode) |
| CE# | Chip Enable Input |
| WE# | Write Enable Input |
| OE# | Output Enable Input |
| BYTE# | Word/Byte Selection Input |
| RESET# | Hardware Reset Pin, Active Low |
| RY/BY# | Ready/Busy Output |
| Vcc | 3.0 volt-only single power supply |
| WP#/ACC | Hardware Write Protect/Acceleration Pin |
| GND | Device Ground |
| NC | Pin Not Connected Internally |

Note: If customers do not need WP#/ACC feature, please connect WP#/ACC pin to VCC or let it floating. The WP#/ACC has an internal pull-up when unconnected WP#/ACC is at Vih.

LOGIC SYMBOL



BLOCK DIAGRAM



BLOCK DIAGRAM DESCRIPTION

The block diagram on Page 9 illustrates a simplified architecture of MX29LV320E T/B. Each block in the block diagram represents one or more circuit modules in the real chip used to access, erase, program, and read the memory array..

The "CONTROL INPUT LOGIC" block receives input pins CE#, OE#, WE#, RESET#, BYTE#, and WP#/ACC. It creates internal timing control signals according to the input pins and outputs to the "ADDRESS LATCH AND BUFFER" to latch the external address pins A0-AM(A20). The internal addresses are output from this block to the main array and decoders composed of "X-DECODER", "Y-DECODER", "Y-PASS GATE", and "FLASH ARRAY". The X-DECODER decodes the word-lines of the flash array, while the Y-DECODER decodes the bit-lines of the flash array. The bit lines are electrically connected to the "SENSE AMPLIFIER" and "PGM DATA HV" selectively through the y-pass gates. Sense amplifiers are used to read out the contents of the flash memory, while the "PGM DATA HV" block is used to selectively deliver high power to bit-lines during programming. The "I/O BUFFER" controls the input and output on the Q0-Q15/A-1 pads. During read operation, the I/O buffer receives data from sense amplifiers and drives the output pads accordingly. In the last cycle of program command, the I/O buffer transmits the data on Q0-Q15/A-1 to "PROGRAM DATA LATCH", which controls the high power drivers in "PGM DATA HV" to selectively program the bits in a word or byte according to the user input pattern.

The "PROGRAM/ERASE HIGH VOLTAGE" block comprises the circuits to generate and deliver the necessary high voltage to the X-DECODER, FLASH ARRAY, and "PGM DATA HV" block. The logic control module comprises of the "WRITE STATE MACHINE (WSM)", "STATE REGISTER", "COMMAND DATA DECODER", and "COMMAND DATA LATCH". When the user issues a command by toggling WE#, the command on Q0-Q15/A-1 is latched in the command data latch and is decoded by the command data decoder. The state register receives the command and records the current state of the device. The WSM implements the internal algorithms for program or erase according to the current command state by controlling each block in the block diagram.

BLOCK STRUCTURE

The main flash memory array can be organized as 4M Bytes x 8 or as 2M Words x 16. The details of the address ranges and the corresponding sector addresses are shown in Table 1. Table 1.a shows the sector group architecture for the Top Boot part, whereas Table 1.b shows the sector group architecture for the Bottom Boot part. The specific security sector addresses are shown at the bottom off each of these tables.

Table 1.a: MX29LV320ET SECTOR GROUP ARCHITECTURE

| Sector Group | Sector Size | | Sector | Sector Address A20-A12 | Address Range | |
|--------------|--------------------|--------------------|--------|------------------------|------------------|------------------|
| | Byte Mode (Kbytes) | Word Mode (Kwords) | | | Byte Mode (x8) | Word Mode (x16) |
| 1 | 64 | 32 | SA0 | 000000xxx | 000000h-00FFFFh | 000000h-07FFFh |
| 1 | 64 | 32 | SA1 | 000001xxx | 010000h-01FFFFh | 008000h-0FFFFh |
| 1 | 64 | 32 | SA2 | 000010xxx | 020000h-02FFFFh | 010000h-17FFFh |
| 1 | 64 | 32 | SA3 | 000011xxx | 030000h-03FFFFh | 018000h-01FFFFh |
| 2 | 64 | 32 | SA4 | 000100xxx | 040000h-04FFFFh | 020000h-027FFFh |
| 2 | 64 | 32 | SA5 | 000101xxx | 050000h-05FFFFh | 028000h-02FFFFh |
| 2 | 64 | 32 | SA6 | 000110xxx | 060000h-06FFFFh | 030000h-037FFFh |
| 2 | 64 | 32 | SA7 | 000111xxx | 070000h-07FFFFh | 038000h-03FFFFh |
| 3 | 64 | 32 | SA8 | 001000xxx | 080000h-08FFFFh | 040000h-047FFFh |
| 3 | 64 | 32 | SA9 | 001001xxx | 090000h-09FFFFh | 048000h-04FFFFh |
| 3 | 64 | 32 | SA10 | 001010xxx | 0A0000h-0AFFFFh | 050000h-057FFFh |
| 3 | 64 | 32 | SA11 | 001011xxx | 0B0000h-0BFFFFh | 058000h-05FFFFh |
| 4 | 64 | 32 | SA12 | 001100xxx | 0C0000h-0CFFFFh | 060000h-067FFFh |
| 4 | 64 | 32 | SA13 | 001101xxx | 0D0000h-0DFFFFh | 068000h-06FFFFh |
| 4 | 64 | 32 | SA14 | 001110xxx | 0E0000h-0EFFFFh | 070000h-077FFFh |
| 4 | 64 | 32 | SA15 | 001111xxx | 0F0000h-0FFFFFFh | 078000h-07FFFFh |
| 5 | 64 | 32 | SA16 | 010000xxx | 100000h-10FFFFh | 080000h-087FFFh |
| 5 | 64 | 32 | SA17 | 010001xxx | 110000h-11FFFFh | 088000h-08FFFFh |
| 5 | 64 | 32 | SA18 | 010010xxx | 120000h-12FFFFh | 090000h-097FFFh |
| 5 | 64 | 32 | SA19 | 010011xxx | 130000h-13FFFFh | 098000h-09FFFFh |
| 6 | 64 | 32 | SA20 | 010100xxx | 140000h-14FFFFh | 0A0000h-0A7FFFh |
| 6 | 64 | 32 | SA21 | 010101xxx | 150000h-15FFFFh | 0A8000h-0AFFFFh |
| 6 | 64 | 32 | SA22 | 010110xxx | 160000h-16FFFFh | 0B0000h-0B7FFFh |
| 6 | 64 | 32 | SA23 | 010111xxx | 170000h-17FFFFh | 0B8000h-0BFFFFh |
| 7 | 64 | 32 | SA24 | 011000xxx | 180000h-18FFFFh | 0C0000h-0C7FFFh |
| 7 | 64 | 32 | SA25 | 011001xxx | 190000h-19FFFFh | 0C8000h-0CFFFFh |
| 7 | 64 | 32 | SA26 | 011010xxx | 1A0000h-1AFFFFh | 0D0000h-0D7FFFh |
| 7 | 64 | 32 | SA27 | 011011xxx | 1B0000h-1BFFFFh | 0D8000h-0DFFFFh |
| 8 | 64 | 32 | SA28 | 011100xxx | 1C0000h-1CFFFFh | 0E0000h-0E7FFFh |
| 8 | 64 | 32 | SA29 | 011101xxx | 1D0000h-1DFFFFh | 0E8000h-0EFFFFh |
| 8 | 64 | 32 | SA30 | 011110xxx | 1E0000h-1EFFFFh | 0F0000h-0F7FFFh |
| 8 | 64 | 32 | SA31 | 011111xxx | 1F0000h-1FFFFFFh | 0F8000h-0FFFFFFh |
| 9 | 64 | 32 | SA32 | 100000xxx | 200000h-20FFFFh | 100000h-107FFFh |
| 9 | 64 | 32 | SA33 | 100001xxx | 210000h-21FFFFh | 108000h-10FFFFh |
| 9 | 64 | 32 | SA34 | 100010xxx | 220000h-22FFFFh | 110000h-117FFFh |



| Sector Group | Sector Size | | Sector | Sector Address A20-A12 | Address Range | |
|--------------|--------------------|--------------------|--------|------------------------|-----------------|-----------------|
| | Byte Mode (Kbytes) | Word Mode (Kwords) | | | Byte Mode (x8) | Word Mode (x16) |
| 9 | 64 | 32 | SA35 | 100011xxx | 230000h-23FFFFh | 118000h-11FFFFh |
| 10 | 64 | 32 | SA36 | 100100xxx | 240000h-24FFFFh | 120000h-127FFFh |
| 10 | 64 | 32 | SA37 | 100101xxx | 250000h-25FFFFh | 128000h-12FFFFh |
| 10 | 64 | 32 | SA38 | 100110xxx | 260000h-26FFFFh | 130000h-137FFFh |
| 10 | 64 | 32 | SA39 | 100111xxx | 270000h-27FFFFh | 138000h-13FFFFh |
| 11 | 64 | 32 | SA40 | 101000xxx | 280000h-28FFFFh | 140000h-147FFFh |
| 11 | 64 | 32 | SA41 | 101001xxx | 290000h-29FFFFh | 148000h-14FFFFh |
| 11 | 64 | 32 | SA42 | 101010xxx | 2A0000h-2AFFFFh | 150000h-157FFFh |
| 11 | 64 | 32 | SA43 | 101011xxx | 2B0000h-2BFFFFh | 158000h-15FFFFh |
| 12 | 64 | 32 | SA44 | 101100xxx | 2C0000h-2CFFFFh | 160000h-167FFFh |
| 12 | 64 | 32 | SA45 | 101101xxx | 2D0000h-2DFFFFh | 168000h-16FFFFh |
| 12 | 64 | 32 | SA46 | 101110xxx | 2E0000h-2EFFFFh | 170000h-177FFFh |
| 12 | 64 | 32 | SA47 | 101111xxx | 2F0000h-2FFFFFh | 178000h-17FFFFh |
| 13 | 64 | 32 | SA48 | 110000xxx | 300000h-30FFFFh | 180000h-187FFFh |
| 13 | 64 | 32 | SA49 | 110001xxx | 310000h-31FFFFh | 188000h-18FFFFh |
| 13 | 64 | 32 | SA50 | 110010xxx | 320000h-32FFFFh | 190000h-197FFFh |
| 13 | 64 | 32 | SA51 | 110011xxx | 330000h-33FFFFh | 198000h-19FFFFh |
| 14 | 64 | 32 | SA52 | 110100xxx | 340000h-34FFFFh | 1A0000h-1A7FFFh |
| 14 | 64 | 32 | SA53 | 110101xxx | 350000h-35FFFFh | 1A8000h-1AFFFFh |
| 14 | 64 | 32 | SA54 | 110110xxx | 360000h-36FFFFh | 1B0000h-1B7FFFh |
| 14 | 64 | 32 | SA55 | 110111xxx | 370000h-37FFFFh | 1B8000h-1BFFFFh |
| 15 | 64 | 32 | SA56 | 111000xxx | 380000h-38FFFFh | 1C0000h-1C7FFFh |
| 15 | 64 | 32 | SA57 | 111001xxx | 390000h-39FFFFh | 1C8000h-1CFFFFh |
| 15 | 64 | 32 | SA58 | 111010xxx | 3A0000h-3AFFFFh | 1D0000h-1D7FFFh |
| 15 | 64 | 32 | SA59 | 111011xxx | 3B0000h-3BFFFFh | 1D8000h-1DFFFFh |
| 16 | 64 | 32 | SA60 | 111100xxx | 3C0000h-3CFFFFh | 1E0000h-1E7FFFh |
| 16 | 64 | 32 | SA61 | 111101xxx | 3D0000h-3DFFFFh | 1E8000h-1EFFFFh |
| 16 | 64 | 32 | SA62 | 111110xxx | 3E0000h-3EFFFFh | 1F0000h-1F7FFFh |
| 17 | 8 | 4 | SA63 | 111111000 | 3F0000h-3F1FFFh | 1F8000h-1F8FFFh |
| 18 | 8 | 4 | SA64 | 111111001 | 3F2000h-3F3FFFh | 1F9000h-1F9FFFh |
| 19 | 8 | 4 | SA65 | 111111010 | 3F4000h-3F5FFFh | 1FA000h-1FAFFFh |
| 20 | 8 | 4 | SA66 | 111111011 | 3F6000h-3F7FFFh | 1FB000h-1FBFFFh |
| 21 | 8 | 4 | SA67 | 111111100 | 3F8000h-3F9FFFh | 1FC000h-1FCFFFh |
| 22 | 8 | 4 | SA68 | 111111101 | 3FA000h-3FBFFFh | 1FD000h-1FDFFFh |
| 23 | 8 | 4 | SA69 | 111111110 | 3FC000h-3FDFFFh | 1FE000h-1FEFFFh |
| 24 | 8 | 4 | SA70 | 111111111 | 3FE000h-3FFFFFh | 1FF000h-1FFFFFh |

Top Boot Security Sector Addresses

| Sector Size | | Address Range | |
|-------------------|-------------------|-----------------|-----------------|
| Byte Mode (bytes) | Word Mode (words) | Byte Mode (x8) | Word Mode (x16) |
| 256 | 128 | 3F0000h-3F00FFh | 1F8000h-1F807Fh |

Table 1.b: MX29LV320EB SECTOR GROUP ARCHITECTURE

| Sector Group | Sector Size | | Sector | Sector Address A20-A12 | Address Range | |
|--------------|--------------------|--------------------|--------|------------------------|-----------------|-----------------|
| | Byte Mode (Kbytes) | Word Mode (Kwords) | | | Byte Mode (x8) | Word Mode (x16) |
| 1 | 8 | 4 | SA0 | 00000000 | 00000h-001FFFh | 00000h-000FFFh |
| 2 | 8 | 4 | SA1 | 00000001 | 002000h-003FFFh | 001000h-001FFFh |
| 3 | 8 | 4 | SA2 | 00000010 | 004000h-005FFFh | 002000h-002FFFh |
| 4 | 8 | 4 | SA3 | 00000011 | 006000h-007FFFh | 003000h-003FFFh |
| 5 | 8 | 4 | SA4 | 00000100 | 008000h-009FFFh | 004000h-004FFFh |
| 6 | 8 | 4 | SA5 | 00000101 | 00A000h-00BFFFh | 005000h-005FFFh |
| 7 | 8 | 4 | SA6 | 00000110 | 00C000h-00DFFFh | 006000h-006FFFh |
| 8 | 8 | 4 | SA7 | 00000111 | 00E000h-00FFFFh | 007000h-007FFFh |
| 9 | 64 | 32 | SA8 | 000001xxx | 010000h-01FFFFh | 008000h-00FFFFh |
| 9 | 64 | 32 | SA9 | 000010xxx | 020000h-02FFFFh | 010000h-017FFFh |
| 9 | 64 | 32 | SA10 | 000011xxx | 030000h-03FFFFh | 018000h-01FFFFh |
| 10 | 64 | 32 | SA11 | 000100xxx | 040000h-04FFFFh | 020000h-027FFFh |
| 10 | 64 | 32 | SA12 | 000101xxx | 050000h-05FFFFh | 028000h-02FFFFh |
| 10 | 64 | 32 | SA13 | 000110xxx | 060000h-06FFFFh | 030000h-037FFFh |
| 10 | 64 | 32 | SA14 | 000111xxx | 070000h-07FFFFh | 038000h-03FFFFh |
| 11 | 64 | 32 | SA15 | 001000xxx | 080000h-08FFFFh | 040000h-047FFFh |
| 11 | 64 | 32 | SA16 | 001001xxx | 090000h-09FFFFh | 048000h-04FFFFh |
| 11 | 64 | 32 | SA17 | 001010xxx | 0A0000h-0AFFFFh | 050000h-057FFFh |
| 11 | 64 | 32 | SA18 | 001011xxx | 0B0000h-0BFFFFh | 058000h-05FFFFh |
| 12 | 64 | 32 | SA19 | 001100xxx | 0C0000h-0CFFFFh | 060000h-067FFFh |
| 12 | 64 | 32 | SA20 | 001101xxx | 0D0000h-0DFFFFh | 068000h-06FFFFh |
| 12 | 64 | 32 | SA21 | 001110xxx | 0E0000h-0EFFFFh | 070000h-077FFFh |
| 12 | 64 | 32 | SA22 | 001111xxx | 0F0000h-0FFFFFh | 078000h-07FFFFh |
| 13 | 64 | 32 | SA23 | 010000xxx | 100000h-10FFFFh | 080000h-087FFFh |
| 13 | 64 | 32 | SA24 | 010001xxx | 110000h-11FFFFh | 088000h-08FFFFh |
| 13 | 64 | 32 | SA25 | 010010xxx | 120000h-12FFFFh | 090000h-097FFFh |
| 13 | 64 | 32 | SA26 | 010011xxx | 130000h-13FFFFh | 098000h-09FFFFh |
| 14 | 64 | 32 | SA27 | 010100xxx | 140000h-14FFFFh | 0A0000h-0A7FFFh |
| 14 | 64 | 32 | SA28 | 010101xxx | 150000h-15FFFFh | 0A8000h-0AFFFFh |
| 14 | 64 | 32 | SA29 | 010110xxx | 160000h-16FFFFh | 0B0000h-0B7FFFh |
| 14 | 64 | 32 | SA30 | 010111xxx | 170000h-17FFFFh | 0B8000h-0BFFFFh |
| 15 | 64 | 32 | SA31 | 011000xxx | 180000h-18FFFFh | 0C0000h-0C7FFFh |
| 15 | 64 | 32 | SA32 | 011001xxx | 190000h-19FFFFh | 0C8000h-0CFFFFh |
| 15 | 64 | 32 | SA33 | 011010xxx | 1A0000h-1AFFFFh | 0D0000h-0D7FFFh |
| 15 | 64 | 32 | SA34 | 011011xxx | 1B0000h-1BFFFFh | 0D8000h-0DFFFFh |
| 16 | 64 | 32 | SA35 | 011100xxx | 1C0000h-1CFFFFh | 0E0000h-0E7FFFh |
| 16 | 64 | 32 | SA36 | 011101xxx | 1D0000h-1DFFFFh | 0E8000h-0EFFFFh |
| 16 | 64 | 32 | SA37 | 011110xxx | 1E0000h-1EFFFFh | 0F0000h-0F7FFFh |
| 16 | 64 | 32 | SA38 | 011111xxx | 1F0000h-1FFFFFh | 0F8000h-0FFFFFh |
| 17 | 64 | 32 | SA39 | 100000xxx | 200000h-20FFFFh | 100000h-107FFFh |
| 17 | 64 | 32 | SA40 | 100001xxx | 210000h-21FFFFh | 108000h-10FFFFh |
| 17 | 64 | 32 | SA41 | 100010xxx | 220000h-22FFFFh | 110000h-117FFFh |



| Sector Group | Sector Size | | Sector | Sector Address A20-A12 | Address Range | |
|--------------|--------------------|--------------------|--------|------------------------|-----------------|-----------------|
| | Byte Mode (Kbytes) | Word Mode (Kwords) | | | Byte Mode (x8) | Word Mode (x16) |
| 17 | 64 | 32 | SA42 | 100011xxx | 230000h-23FFFFh | 118000h-11FFFFh |
| 18 | 64 | 32 | SA43 | 100100xxx | 240000h-24FFFFh | 120000h-127FFFh |
| 18 | 64 | 32 | SA44 | 100101xxx | 250000h-25FFFFh | 128000h-12FFFFh |
| 18 | 64 | 32 | SA45 | 100110xxx | 260000h-26FFFFh | 130000h-137FFFh |
| 18 | 64 | 32 | SA46 | 100111xxx | 270000h-27FFFFh | 138000h-13FFFFh |
| 19 | 64 | 32 | SA47 | 101000xxx | 280000h-28FFFFh | 140000h-147FFFh |
| 19 | 64 | 32 | SA48 | 101001xxx | 290000h-29FFFFh | 148000h-14FFFFh |
| 19 | 64 | 32 | SA49 | 101010xxx | 2A0000h-2AFFFFh | 150000h-157FFFh |
| 19 | 64 | 32 | SA50 | 101011xxx | 2B0000h-2BFFFFh | 158000h-15FFFFh |
| 20 | 64 | 32 | SA51 | 101100xxx | 2C0000h-2CFFFFh | 160000h-167FFFh |
| 20 | 64 | 32 | SA52 | 101101xxx | 2D0000h-2DFFFFh | 168000h-16FFFFh |
| 20 | 64 | 32 | SA53 | 101110xxx | 2E0000h-2EFFFFh | 170000h-177FFFh |
| 20 | 64 | 32 | SA54 | 101111xxx | 2F0000h-2FFFFFh | 178000h-17FFFFh |
| 21 | 64 | 32 | SA55 | 110000xxx | 300000h-30FFFFh | 180000h-187FFFh |
| 21 | 64 | 32 | SA56 | 110001xxx | 310000h-31FFFFh | 188000h-18FFFFh |
| 21 | 64 | 32 | SA57 | 110010xxx | 320000h-32FFFFh | 190000h-197FFFh |
| 21 | 64 | 32 | SA58 | 110011xxx | 330000h-33FFFFh | 198000h-19FFFFh |
| 22 | 64 | 32 | SA59 | 110100xxx | 340000h-34FFFFh | 1A0000h-1A7FFFh |
| 22 | 64 | 32 | SA60 | 110101xxx | 350000h-35FFFFh | 1A8000h-1AFFFFh |
| 22 | 64 | 32 | SA61 | 110110xxx | 360000h-36FFFFh | 1B0000h-1B7FFFh |
| 22 | 64 | 32 | SA62 | 110111xxx | 370000h-37FFFFh | 1B8000h-1BFFFFh |
| 23 | 64 | 32 | SA63 | 111000xxx | 380000h-38FFFFh | 1C0000h-1C7FFFh |
| 23 | 64 | 32 | SA64 | 111001xxx | 390000h-39FFFFh | 1C8000h-1CFFFFh |
| 23 | 64 | 32 | SA65 | 111010xxx | 3A0000h-3AFFFFh | 1D0000h-1D7FFFh |
| 23 | 64 | 32 | SA66 | 111011xxx | 3B0000h-3BFFFFh | 1D8000h-1DFFFFh |
| 24 | 64 | 32 | SA67 | 111100xxx | 3C0000h-3CFFFFh | 1E0000h-1E7FFFh |
| 24 | 64 | 32 | SA68 | 111101xxx | 3D0000h-3DFFFFh | 1E8000h-1EFFFFh |
| 24 | 64 | 32 | SA69 | 111110xxx | 3E0000h-3EFFFFh | 1F0000h-1F7FFFh |
| 24 | 64 | 32 | SA70 | 111111xxx | 3F0000h-3FFFFFh | 1F8000h-1FFFFFh |

Bottom Boot Security Sector Addresses

| Sector Size | | Address Range | |
|-------------------|-------------------|-----------------|-----------------|
| Byte Mode (bytes) | Word Mode (words) | Byte Mode (x8) | Word Mode (x16) |
| 256 | 128 | 000000h-0000FFh | 000000h-00007Fh |

BUS OPERATION

Table 2-1. BUS OPERATION

| Mode Select | RE-SET# | CE# | WE# | OE# | Address | Data (I/O) Q7~Q0 | Byte# | | WP#/ACC |
|----------------------------------|------------|------------|-----|-----|--|---------------------|---------|-------|---------|
| | | | | | | | Vil | Vih | |
| | | | | | | | Q15~Q8 | | |
| Device Reset | L | X | X | X | X | HighZ | HighZ | HighZ | L/H |
| Standby Mode | Vcc ± 0.3V | Vcc ± 0.3V | X | X | X | HighZ | HighZ | HighZ | H |
| Output Disable | H | L | H | H | X | HighZ | HighZ | HighZ | L/H |
| Read Mode | H | L | H | L | AIN | DOUT | Q8-Q14= | DOUT | L/H |
| Write (Note1) | H | L | L | H | AIN | DIN | HighZ | DIN | Note3 |
| Accelerate Program | H | L | L | H | AIN | DIN | Q15=A-1 | DIN | Vhv |
| Temporary Sector-Group Unprotect | Vhv | X | X | X | AIN | DIN | HighZ | DIN | Note3 |
| Sector-Group Protect (Note2) | Vhv | L | L | H | Sector Address, A6=L, A1=H, A0=L | DIN, DOUT | X | X | L/H |
| Chip Unprotect (Note2) | Vhv | L | L | H | Sector Address, A6=H, A1=H, A0=L | DIN, DOUT | X | X | Note3 |

Notes:

1. All sectors will be unprotected if WP#/ACC=Vhv.
2. The two outmost boot sectors are protected if WP#/ACC=Vil.
3. When WP#/ACC = Vih, the protection conditions of the two outmost boot sectors depend on previous protection conditions."Sector/Sector Block Protection and Unprotection" describes the protect and unprotect method.
4. Q0~Q15 are input (DIN) or output (DOUT) pins according to the requests of command sequence, sector protection, or data polling algorithm.
5. In Word Mode (Byte#=Vih), the addresses are AM to A0.
In Byte Mode (Byte#=Vil), the addresses are AM to A-1 (Q15).
6. AM: MSB of address.

Table 2-2. BUS OPERATION

| Item | Control Input | | | AM to A12 | A11 to A10 | A9 | A8 to A7 | A6 | A5 to A2 | A1 | A0 | Q7~Q0 | Q15~Q8 |
|---|---------------|-----|-----|-----------------|------------------|-----------------|----------------|----|----------------|----|----|------------------------|-----------------------|
| | CE# | WE# | OE# | | | | | | | | | | |
| Sector Lock Status Verification | L | H | L | SA | x | V _{hv} | x | L | x | H | L | 01h or 00h (Note 1) | x |
| Read Silicon ID Manufacturer Code | L | H | L | x | x | V _{hv} | x | L | x | L | L | C2h | x |
| Read Silicon ID MX29LV320ET | L | H | L | x | x | V _{hv} | x | L | x | L | H | A7h | 22h(Word) x (Byte) |
| Read Silicon ID MX29LV320EB | L | H | L | x | x | V _{hv} | x | L | x | L | H | A8h | 22h(Word) x (Byte) |
| Read Indicator Bit (Q7) For Security Sector | L | H | L | x | x | V _{hv} | x | L | x | H | H | 99h or 19h (Note 2) | x |

Notes:

1. Sector unprotected code:00h. Sector protected code:01h.
2. Factory locked code: 99h. Factory unlocked code: 19h.
3. AM: MSB of address.

FUNCTIONAL OPERATION DESCRIPTION

READ OPERATION

To perform a read operation, the system addresses the desired memory array or status register location by providing its address on the address pins and simultaneously enabling the chip by driving CE# & OE# LOW, and WE# HIGH. After the Tce and Toa timing requirements have been met, the system can read the contents of the addressed location by reading the Data (I/O) pins. If either the CE# or OE# is held HIGH, the outputs will remain tri-stated and no data will appear on the output pins.

WRITE OPERATION

To perform a write operation, the system provides the desired address on the address pins, enables the chip by asserting CE# LOW, and disables the Data (I/O) pins by holding OE# HIGH. The system then places data to be written on the Data (I/O) pins and pulses WE# LOW. The device captures the address information on the falling edge of WE# and the data on the rising edge of WE#. To see an example, please refer to the timing diagram in [Figure 1](#). The system is not allowed to write invalid commands (commands not defined in this datasheet) to the device. Writing an invalid command may put the device in an undefined state.

DEVICE RESET

Driving the RESET# pin LOW for a period of Trp or more will return the device to Read mode. If the device is in the middle of a program or erase operation, the reset operation will take at most a period of Tready1 before the device returns to Read mode. Until the device does returns to Read mode, the RY/BY# pin will remain Low (Busy Status).

When the RESET# pin is held at GND±0.3V, the device only consumes standby (Isbr) current. However, the device draws larger current if the RESET# pin is held at a voltage greater than GND+0.3V and less than or equal to Vil.

It is recommended to tie the system reset signal to the RESET# pin of the flash memory. This allows the device to be reset with the system and puts it in a state where the system can immediately begin reading boot code from it.

STANDBY MODE

The device enters Standby mode whenever the RESET# and CE# pins are both held High. While in this mode, WE# and OE# will be ignored, all Data Output pins will be in a high impedance state, and the device will draw minimal (Isb) current.

OUTPUT DISABLE

While in active mode (RESET# HIGH and CE# LOW), the OE# pin controls the state of the output pins. If OE# is held HIGH, all Data (I/O) pins will remain tri-stated. If held LOW, the Byte or Word Data (I/O) pins will drive data.

FUNCTIONAL OPERATION DESCRIPTION (cont'd)

BYTE/WORD SELECTION

The BYTE# input pin is used to select the organization of the array data and how the data is input/output on the Data (I/O) pins. If the BYTE# pin is held HIGH, Word mode will be selected and all 16 data lines (Q15 to Q0) will be active.

If BYTE# is forced LOW, Byte mode will be active and only data lines Q7 to Q0 will be active. Data lines Q8 to Q14 will remain in a high impedance state and Q15 becomes the A-1 address input pin.

HARDWARE WRITE PROTECT

By driving the WP#/ACC pin LOW, the outermost two boot sectors are protected from all erase/program operations. If WP#/ACC is held HIGH (Vih to VCC), these two outermost sectors revert to their previously protected/unprotected status.

ACCELERATED PROGRAMMING OPERATION

By applying high voltage (Vhv) to the WP#/ACC pin, the device will enter the Accelerated Programming mode. This mode permits the system to skip the normal command unlock sequences and program byte/word locations directly. During accelerated programming, the current drawn from the WP#/ACC pin is no more than Icp1.

TEMPORARY SECTOR GROUP UNPROTECT OPERATION

The system can apply Vhv to the RESET# pin to place the device in Temporary Unprotect mode. In this mode, previously protected sectors can be programmed/erased just as though they were unprotected. The device returns to normal operation once Vhv is removed from the RESET# pin and previously protected sectors will once again be protected.

SECTOR GROUP PROTECT OPERATION

The MX29LV320E T/B provides user programmable protection against program/erase operations for selected sectors. Most sectors cannot be protected individually. Instead, they are bound in groups of four or less called Sector-Groups. Protection is available for individual Sector-Groups, which includes all member sectors. Boot sectors are the exception to this rule as they are assigned unique Sector-Group addresses and can be protected individually without protecting any adjacent sectors or Sector-Groups. The three sectors adjacent to the boot sectors form a non-standard Sector-Group. Please refer to Table 1a and Table 1b which show all Sector-Group assignments.

During the protection operation, the sector address of any sector within a Sector-Group may be used to specify the Sector-Group being protected.

There are two methods available to protect Sector-Groups. The first and preferred method is activated by applying Vhv on the RESET# pin and following the timing in [Figure 13](#) and the algorithm shown in [Figure 14](#). This is a command operation that can be performed either on an external programmer or in-circuit by the system controller. The second method is strictly a bus operation and is entered by asserting Vhv on A9 and OE# pins, with A6 and CE# at Vil. The protection operation begins at the falling edge of WE# and terminates at the rising edge. Contact Macronix for more details on this method.

FUNCTIONAL OPERATION DESCRIPTION (cont'd)

CHIP UNPROTECT OPERATION

The Chip Unprotect operation unprotects all sectors within the device. It is standard procedure and highly recommended to protect all Sector-Groups prior using the Chip Unprotect operation. This will prevent possible damage to the Sector-Group protection logic. All Sector Groups are unprotected when shipped from the factory, so this operation is only necessary if the user has previously protected any Sector-Groups and wishes to unprotect them now.

MX29LV320E T/B provides two methods for unprotecting the entire chip. The first and preferred method is entered by applying V_hv on RESET# pin and following the timing diagram in [Figure 13](#) and using the algorithm shown in [Figure 15](#).

The second method is entered by asserting V_hv on A9 and OE# pins, with A6 at V_{ih} and CE# at V_{il}. The protection operation begins at the falling edge of WE# and terminates at the rising edge. Contact Macronix for more details on this method.

AUTOMATIC SELECT BUS OPERATIONS

The following five bus operations require A9 to be raised to V_hv. Please see AUTOMATIC SELECT COMMAND SEQUENCE in the COMMAND OPERATIONS section for details of equivalent command operations that do not require the use of V_hv.

SECTOR LOCK STATUS VERIFICATION

To determine the protected state of any sector using bus operations, the system performs a READ OPERATION with A9 raised to V_hv, the sector address applied to address pins A20 to A12, address pins A6 & A0 held LOW, and address pin A1 held HIGH. If data bit Q0 is LOW, the sector is not protected, and if Q0 is HIGH, the sector is protected.

READ SILICON ID MANUFACTURER CODE

To determine the Silicon ID Manufacturer Code, the system performs a READ OPERATION with A9 raised to V_hv and address pins A6, A1, & A0 held LOW. The Macronix ID code of C2h should be present on data bits Q7 to Q0.

READ SILICON ID MX29LV320ET CODE

To verify the Silicon ID MX29LV320ET Code, the system performs a READ OPERATION with A9 raised to V_hv, address pins A6 & A1 held LOW, and address pin A0 held HIGH. The MX29LV320ET code of A7h should be present on data bits Q7 to Q0. Q15 to Q8 will be tri-stated unless Word mode is selected. In this case, Q15 to Q8 will output the value 22h.

READ SILICON ID MX29LV320EB CODE

To verify the Silicon ID MX29LV320EB Code, the system performs a READ OPERATION with A9 raised to V_hv, address pins A6 & A1 held LOW, and address pin A0 held HIGH. The MX29LV320ET code of A8h should be present on data bits Q7 to Q0. Q15 to Q8 will be tri-stated unless Word mode is selected. In this case, Q15 to Q8 will output the code 22h.

FUNCTIONAL OPERATION DESCRIPTION (cont'd)**READ INDICATOR BIT (Q7) FOR SECURITY SECTOR**

To determine if the Security Sector has been locked at the factory, the system performs a READ OPERATION with A9 raised to V_{hv}, address pin A6 held LOW, and address pins A1 & A0 held HIGH. If the Security Sector has been locked at the factory, the code 99h will be present on data bits Q7 to Q0. Otherwise, the factory unlocked code of 19h will be present.

INHERENT DATA PROTECTION

To avoid accidental erasure or programming of the device, the device is automatically reset to Read mode during power up. Additionally, the following design features protect the device from unintended data corruption.

COMMAND COMPLETION

Only after the successful completion of the specified command sets will the device begin its erase or program operation. If any command sequence is interrupted or given an invalid command, the device immediately returns to Read mode.

LOW VCC WRITE INHIBIT

The device refuses to accept any write command when V_{cc} is less than V_{Iko}. This prevents data from spuriously being altered during power-up, power-down, or temporary power interruptions. The device automatically resets itself when V_{cc} is lower than V_{Iko} and write cycles are ignored until V_{cc} is greater than V_{Iko}. The system must provide proper signals on control pins after V_{cc} rises above V_{Iko} to avoid unintentional program or erase operations.

WRITE PULSE "GLITCH" PROTECTION

CE#, WE#, OE# pulses shorter than 5ns are treated as glitches and will not be regarded as an effective write cycle.

LOGICAL INHIBIT

A valid write cycle requires both CE# and WE# at V_{il} with OE# at V_{ih}. Write cycle is ignored when either CE# at V_{ih}, WE# at V_{ih}, or OE# at V_{il}.

POWER-UP SEQUENCE

Upon power up, the MX29LV320E T/B is placed in Read mode. Furthermore, program or erase operation will begin only after successful completion of specified command sequences.



FUNCTIONAL OPERATION DESCRIPTION (cont'd)

POWER-UP WRITE INHIBIT

When WE#, CE# is held at V_{il} and OE# is held at V_{ih} during power up, the device ignores the first command on the rising edge of WE#.

POWER SUPPLY DECOUPLING

A 0.1 μ F capacitor should be connected between the Vcc and GND to reduce the noise effect.

COMMAND OPERATIONS

TABLE 3. MX29LV320E T/B COMMAND DEFINITIONS

| Command | | Read Mode | Reset Mode | Automatic Select | | | | | | | | Enter Security Sector Region Enable | |
|---------------|------|-----------|------------|------------------|------|-----------|------|----------------|-------|-----------------------|--------------|-------------------------------------|------|
| | | | | Manufacture ID | | Device ID | | Sector Factory | | Sector Protect Verify | | Word | Byte |
| | | | | Word | Byte | Word | Byte | Word | Byte | Word | Byte | | |
| 1st Bus Cycle | Addr | Addr | XXX | 555 | AAA | 555 | AAA | 555 | AAA | 555 | AAA | 555 | AAA |
| | Data | Data | F0 | AA | AA | AA | AA | AA | AA | AA | AA | AA | AA |
| 2nd Bus Cycle | Addr | | | 2AA | 555 | 2AA | 555 | 2AA | 555 | 2AA | 555 | 2AA | 555 |
| | Data | | | 55 | 55 | 55 | 55 | 55 | 55 | 55 | 55 | 55 | 55 |
| 3rd Bus Cycle | Addr | | | 555 | AAA | 555 | AAA | 555 | AAA | 555 | AAA | 555 | AAA |
| | Data | | | 90 | 90 | 90 | 90 | 90 | 90 | 90 | 90 | 88 | 88 |
| 4th Bus Cycle | Addr | | | X00 | X00 | X01 | X02 | X03 | X06 | (Sector) X02 | (Sector) X04 | | |
| | Data | | | C2h | C2h | ID | ID | 99/19 | 99/19 | 00/01 | 00/01 | | |
| 5th Bus Cycle | Addr | | | | | | | | | | | | |
| | Data | | | | | | | | | | | | |
| 6th Bus Cycle | Addr | | | | | | | | | | | | |
| | Data | | | | | | | | | | | | |

| Command | | Exit Security Sector | | Program | | Chip Erase | | Sector Erase | | CFI Read | | Erase Suspend | Erase Resume |
|---------------|------|----------------------|------|---------|------|------------|------|--------------|--------|----------|------|---------------|--------------|
| | | Word | Byte | Word | Byte | Word | Byte | Word | Byte | Word | Byte | Byte/Word | Byte/Word |
| 1st Bus Cycle | Addr | 555 | AAA | 555 | AAA | 555 | AAA | 555 | AAA | 55 | AA | XXX | XXX |
| | Data | AA | AA | AA | AA | AA | AA | AA | AA | 98 | 98 | B0 | 30 |
| 2nd Bus Cycle | Addr | 2AA | 555 | 2AA | 555 | 2AA | 555 | 2AA | 555 | | | | |
| | Data | 55 | 55 | 55 | 55 | 55 | 55 | 55 | 55 | | | | |
| 3rd Bus Cycle | Addr | 555 | AAA | 555 | AAA | 555 | AAA | 555 | AAA | | | | |
| | Data | 90 | 90 | A0 | A0 | 80 | 80 | 80 | 80 | | | | |
| 4th Bus Cycle | Addr | XXX | XXX | Addr | Addr | 555 | AAA | 555 | AAA | | | | |
| | Data | 00 | 00 | Data | Data | AA | AA | AA | AA | | | | |
| 5th Bus Cycle | Addr | | | | | 2AA | 555 | 2AA | 555 | | | | |
| | Data | | | | | 55 | 55 | 55 | 55 | | | | |
| 6th Bus Cycle | Addr | | | | | 555 | AAA | Sector | Sector | | | | |
| | Data | | | | | 10 | 10 | 30 | 30 | | | | |

Notes:

1. ID 22A7h(Top), 22A8h(Bottom).
2. It is not allowed to adopt any other code which is not in the above command definition table.

COMMAND OPERATIONS (cont'd)**AUTOMATIC PROGRAMMING OF THE MEMORY ARRAY**

The MX29LV320E T/B provides the user the ability to program the memory array in Byte mode or Word mode. As long as the users enters the correct cycle defined in the [Table 3](#) (including 2 unlock cycles and the A0H program command), any byte or word data provided on the data lines by the system will automatically be programmed into the array at the specified location.

After the program command sequence has been executed, the internal write state machine (WSM) automatically executes the algorithms and timings necessary for programming and verification, which includes generating suitable program pulses, checking cell threshold voltage margins, and repeating the program pulse if any cells do not pass verification or have low margins. The internal controller protects cells that do pass verification and margin tests from being over-programmed by inhibiting further program pulses to these passing cells as weaker cells continue to be programmed.

With the internal WSM automatically controlling the programming process, the user only needs to enter the program command and data once.

Programming will only change the bit status from "1" to "0". It is not possible to change the bit status from "0" to "1" by programming. This can only be done by an erase operation. Furthermore, the internal write verification only checks and detects errors in cases where a "1" is not successfully programmed to "0".

Any commands written to the device during programming will be ignored except hardware reset, which will terminate the program operation after a period of time no more than Tready1. When the embedded program algorithm is complete or the program operation is terminated by a hardware reset, the device will return to Read mode.

The typical chip program time at room temperature of the MX29LV320E T/B is less than 36 seconds.

After the embedded program operation has begun, the user can check for completion by reading the following bits in the status register:

| Status | Q7*1 | Q6*1 | Q5 | RY/BY# *2 |
|-------------------|------|---------------|----|-----------|
| In progress | Q7# | Toggling | 0 | 0 |
| Finished | Q7 | Stop toggling | 0 | 1 |
| Exceed time limit | Q7# | Toggling | 1 | 0 |

*1: When an attempt is made to program a protected sector, the program operation will abort thus preventing any data changes in the protected sector. Q7 will output complement data and Q6 will toggle (briefly 1us or less) before aborting and returning the device to Read mode.

*2: RY/BY# is an open drain output pin and should be connected to VCC through a high value pull-up resistor.

ERASING THE MEMORY ARRAY

There are two types of erase operations performed on the memory array -- Sector Erase and Chip Erase. In the Sector Erase operation, one or more selected sectors may be erased simultaneously. In the Chip Erase operation, the complete memory array is erased except for any protected sectors.

COMMAND OPERATIONS (cont'd)**SECTOR ERASE**

The sector erase operation is used to clear data within a sector by returning all of its memory locations to the "1" state. It requires six command cycles to initiate the erase operation. The first two cycles are "unlock cycles", the third is a configuration cycle, the fourth and fifth are also "unlock cycles", and the sixth cycle is the Sector Erase command. After the sector erase command sequence has been issued, an internal 50us time-out counter is started. Until this counter reaches zero, additional sector addresses and Sector Erase commands may be issued thus allowing multiple sectors to be selected and erased simultaneously. After the 50us time-out counter has expired, no new commands will be accepted and the embedded sector erase operation will begin. Note that the 50us timer-out counter is restarted after every erase command sequence. If the user enters any command other than Sector Erase or Erase Suspend during the time-out period, the erase operation will abort and the device will return to Read mode.

After the embedded sector erase operation begins, all commands except Erase Suspend will be ignored. The only way to interrupt the operation is with an Erase Suspend command or with a hardware reset. The hardware reset will completely abort the operation and return the device to Read mode.

The system can determine the status of the embedded sector erase operation by the following methods:

| Status | Q7 | Q6 | Q5 | Q3 (note 1) | Q2 | RY/BY# (note 2) |
|---------------------|----|---------------|----|-------------|----------|-----------------|
| Time-out period | 0 | Toggling | 0 | 0 | Toggling | 0 |
| In progress | 0 | Toggling | 0 | 1 | Toggling | 0 |
| Finished | 1 | Stop toggling | 0 | 1 | 1 | 1 |
| Exceeded time limit | 0 | Toggling | 1 | 1 | Toggling | 0 |

Note :

1. The Q3 status bit is the time-out indicator. When Q3=0, the time-out counter has not yet reached zero and a new Sector Erase command may be issued to specify the address of another sector to be erased. When Q3=1, the time-out counter has expired and the Sector Erase operation has already begun. Erase Suspend is the only valid command that may be issued once the embedded erase operation is underway.
2. RY/BY# is an open drain output pin and should be connected to VCC through a high value pull-up resistor.
3. When an attempt is made to erase only protected sector(s), the program operation will abort thus preventing any data changes in the protected sector(s). Q7 will output zero and Q6 will toggle (briefly 100us or less) before aborting and returning the device to read mode. If unprotected sectors are also specified, however, they will be erased normally and the protected sector(s) will remain unchanged.
4. Q2 is a localized indicator showing a specified sector is undergoing erase operation or not. Q2 toggles when user reads at addresses where the sectors are actively being erased (in erase mode) or to be erased (in erase suspend mode). When a sector has been completely erased, Q2 stops toggling at the sector even when the device is still in erase operation for remaining selected sectors. At that circumstance, Q2 will still toggle when device is read at any other sector that remains to be erased.

COMMAND OPERATIONS (cont'd)**CHIP ERASE**

The Chip Erase operation is used to erase all the data within the memory array. All memory cells containing a "0" will be returned to the erased state of "1". This operation requires 6 write cycles to initiate the action. The first two cycles are "unlock" cycles, the third is a configuration cycle, the fourth and fifth are also "unlock" cycles, and the sixth cycle initiates the chip erase operation.

During the chip erase operation, no other software commands will be accepted, but if a hardware reset is received or the working voltage is too low, that chip erase will be terminated. After Chip Erase, the chip will automatically return to Read mode.

The system can determine the status of the embedded chip erase operation by the following methods:

| Status | Q7 | Q6 | Q5 | Q2 | RY/BY# ^{*1} |
|-------------------|----|---------------|----|----------|----------------------|
| In progress | 0 | Toggling | 0 | Toggling | 0 |
| Finished | 1 | Stop toggling | 0 | 1 | 1 |
| Exceed time limit | 0 | Toggling | 1 | Toggling | 0 |

*1: RY/BY# is an open drain output pin and should be connected to VCC through a high value pull-up resistor.

SECTOR ERASE SUSPEND

After beginning a sector erase operation, Erase Suspend is the only valid command that may be issued. If the system issues an Erase Suspend command during the 50us time-out period following a Sector Erase command, the time-out period will terminate immediately and the device will enter Erase-Suspended Read mode. If the system issues an Erase Suspend command after the sector erase operation has already begun, the device will not enter Erase-Suspended Read mode until Tready1 time has elapsed. The system can determine if the device has entered the Erase-Suspended Read mode through Q6, Q7, and RY/BY#.

After the device has entered Erase-Suspended Read mode, the system can read or program any sector(s) except those being erased by the suspended erase operation. Reading any sector being erased or programmed will return the contents of the status register. Whenever a suspend command is issued, the user must issue a resume command and check Q6 toggle bit status, before issuing another erase command. The system can use the status register bits shown in the following table to determine the current state of the device:

| Status | Q7 | Q6 | Q5 | Q3 | Q2 | RY/BY# |
|---|------|-----------|------|------|--------|--------|
| Erase suspend read in erase suspended sector | 1 | No toggle | 0 | N/A | Toggle | 1 |
| Erase suspend read in non-erase suspended sector | Data | Data | Data | Data | Data | 1 |
| Erase suspend program in non-erase suspended sector | Q7# | Toggle | 0 | N/A | N/A | 0 |

When the device has suspended erasing, the user can execute the command sets except sector erase and chip erase, such as read silicon ID, sector protect verify, program, CFI query and erase resume.

COMMAND OPERATIONS (cont'd)**SECTOR ERASE RESUME**

The sector Erase Resume command is valid only when the device is in Erase-Suspended Read mode. After erase resumes, the user can issue another Erase Suspend command, but there should be a 4ms interval between Erase Resume and the next Erase Suspend command. If the user enters an infinite suspend-resume loop, or suspend-resume exceeds 1024 times, erase times will increase dramatically.

AUTOMATIC SELECT OPERATIONS

When the device is in Read mode, Erase-Suspended Read mode, or CFI mode, the user can issue the Automatic Select command shown in Table 3 (two unlock cycles followed by the Automatic Select command 90h) to enter Automatic Select mode. After entering Automatic Select mode, the user can query the Manufacturer ID, Device ID, Security Sector locked status, or Sector-Group protected status multiple times without issuing a new Automatic Select command.

While In Automatic Select mode, issuing a Reset command (F0h) will return the device to Read mode (or Erase-Suspended Read mode if Erase-Suspend was active).

Another way to enter Automatic Select mode is to use one of the bus operations shown in [Table 2-2](#). BUS OPERATION. After the high voltage (V_{hv}) is removed from the A9 pin, the device will automatically return to Read mode or Erase-Suspended Read mode.

AUTOMATIC SELECT COMMAND SEQUENCE

Automatic Select mode is used to access the manufacturer ID, device ID and to verify whether or not secured silicon is locked and whether or not a sector is protected. The automatic select mode has four command cycles. The first two are unlock cycles, and followed by a specific command. The fourth cycle is a normal read cycle, and user can read at any address any number of times without entering another command sequence. The Reset command is necessary to exit the Automatic Select mode and back to read array. The following table shows the identification code with corresponding address.

| | Address (Hex) | | Data (Hex) | Representation |
|-----------------------|---------------|-----------------------|------------|-------------------------|
| Manufacturer ID | Word | X00 | C2 | |
| | Byte | X00 | C2 | |
| Device ID | Word | X01 | 22A7/22A8 | Top/Bottom Boot Sector |
| | Byte | X02 | A7/A8 | Top/Bottom Boot Sector |
| Secured Silicon | Word | X03 | 99/19 | Factory locked/unlocked |
| | Byte | X06 | 99/19 | Factory locked/unlocked |
| Sector Protect Verify | Word | (Sector address) X 02 | 00/01 | Unprotected/protected |
| | Byte | (Sector address) X 04 | 00/01 | Unprotected/protected |

After entering automatic select mode, no other commands are allowed except the reset command.

COMMAND OPERATIONS (cont'd)

READ MANUFACTURER ID OR DEVICE ID

The Manufacturer ID (identification) is a unique hexadecimal number assigned to each manufacturer by the JEDEC committee. Each company has its own manufacturer ID, which is different from the ID of all other companies. The number assigned to Macronix is C2h.

The Device ID is a unique hexadecimal number assigned by the manufacturer for each one of the flash devices made by that manufacturer.

The above two ID types are stored in a 16-bit register on the flash device -- eight bits for each ID. This register is normally read by the user or by the programming machine to identify the manufacturer and the specific device.

After entering Automatic Select mode, performing a read operation with A1 & A0 held LOW will cause the device to output the Manufacturer ID on the Data I/O (Q7 to Q0) pins. Performing a read operation with A1 LOW and A0 HIGH will cause the device to output the Device ID.

SECURITY SECTOR LOCK STATUS

After entering Automatic Select mode, the customer can check the lock status of the Security Sector by performing a read operations with A0 and A1 held HIGH. If the code 99h is read from data pins Q7 to Q0, the sector has been locked at the factory. If the code 19h is read, the sector has not been locked at the factory.

VERIFY SECTOR GROUP PROTECTION

After entering Automatic Select mode, performing a read operation with A1 held HIGH and A0 held LOW and the address of the sector to be checked applied to A20 to A12, data bit Q0 will indicate the protected status of the addressed sector. If Q0 is HIGH, the sector is protected. Conversely, if Q0 is LOW, the sector is unprotected.

SECURITY SECTOR FLASH MEMORY REGION

The Security Sector region is an extra OTP memory space of 256Bytes (128Words) in length. The Security Sector can be locked by the factory prior to shipping, or it can be locked by the customer later.

In factory-locked device, security sector region is protected when shipped from factory and the security silicon sector indicator bit, Q7 (at autoselect address 03h) is set to "1". In customer lockable device, security sector region is unprotected when shipped from factory and the security silicon indicator bit is set to "0".

FACTORY LOCKED: SECURITY SECTOR PROGRAMMED AND PROTECTED AT THE FACTORY

In a factory locked device, the Security Sector is permanently locked before shipping from the factory. The device will have a 16-byte (8-word) ESN in the security region. In bottom boot devices, the ESN occupies addresses 00000h to 0000Fh in byte mode or 00000h to 00007h in word mode. In top boot devices, the ESN occupies addresses 3F0000h to 3F000Fh in byte mode or 1F8000h to 1F8007h in word mode.

COMMAND OPERATIONS (cont'd)

CUSTOMER LOCKABLE: SECURITY SECTOR NOT PROGRAMMED OR PROTECTED AT THE FACTORY

When the security feature is not required, the Security Sector can provide an extra sector of memory.

Two methods are available for protecting the Security Sector. Note that once the Security Sector is protected, there is NO way to unprotect it and its contents can no longer be altered.

The first protection method requires writing the three-cycle Enter Security Region command followed by the use of the Sector-Group protect algorithm as illustrated in [Figure 14](#) with the following exception: the RESET# pin may be at either Vih or Vhv. Unlike normal Sector-Groups, which do require Vhv on the RESET# pin, the Security Sector may be permanently locked in-circuit without the use of high voltage.

The second protection method also uses the three-cycle Enter Security Region command, but uses bus operations that applies Vhv to the A9 and OE# pins with A6, CE#, and WE# held LOW and the SA address applied to A20 to A12. The protection operation begins at the falling edge of WE# and terminates at the rising edge. Contact Macronix for more details on using this method.

After the Security Sector is locked and verified, the system must write an Exit Security Sector Region command, go through a power cycle, or issue a hardware reset to return the device to read normal array mode.

ENTER AND EXIT SECURITY SECTOR

The device allows the user to access the extra 256-Byte sector identified as the Security Sector, which may contain a random, 128-bits electronic serial number (ESN), or it may contain user data.

To access the Security Sector, the user must issue a three-cycle "Enter Security Sector" command sequence. To exit the Security Sector and return to normal operation, the user issues the four-cycle "Exit Security Sector" command. Before issuing the "Exit Security Sector" command, please ensure the entering of security sector region.

COMMAND OPERATIONS (cont'd)**RESET OPERATION**

In the following situations, executing reset command will reset device back to Read mode:

- Among erase command sequence (before the full command set is completed)
- Sector erase time-out period
- Erase fail (while Q5 is high)
- Among program command sequence (before the full command set is completed, erase-suspended program included)
- Program fail (while Q5 is high, and erase-suspended program fail is included)
- Read silicon ID mode
- Sector protect verify
- CFI mode

While device is at the status of program fail or erase fail (Q5 is high), user must issue reset command to reset device back to read array mode. While the device is in read silicon ID mode, sector protect verify or CFI mode, user must issue reset command to reset device back to read array mode.

When the device is in the progress of programming (not program fail) or erasing (not erase fail), device will ignore reset command.

COMMON FLASH MEMORY INTERFACE (CFI) MODE

QUERY COMMAND AND COMMAND FLASH MEMORY INTERFACE (CFI) MODE

MX29LV320E T/B features CFI mode. Host system can retrieve the operating characteristics, structure and vendor-specified information such as identifying information, memory size, byte/word configuration, operating voltages and timing information of this device by CFI mode. The device enters the CFI Query mode when the system writes the CFI Query command, 98H, to address 55h/AAh (depending on Word/Byte mode) any time the device is ready to read array data. The system can read CFI information at the addresses given in Table 4.

Once user enters CFI query mode, user can not issue any other commands except reset command. The reset command is required to exit CFI mode and go back to the mode before entering CFI. The system can write the CFI Query command only when the device is in read mode, erase suspend, standby mode or automatic select mode. The CFI unused area is Macronix's reserved.

Table 4-1. CFI mode: Identification Data Values
(All values in these tables are in hexadecimal)

| Description | Address (h) (Word Mode) | Address (h) (Byte Mode) | Data (h) |
|--|----------------------------|----------------------------|----------|
| Query-unique ASCII string "QRY" | 10 | 20 | 0051 |
| | 11 | 22 | 0052 |
| | 12 | 24 | 0059 |
| Primary vendor command set and control interface ID code | 13 | 26 | 0002 |
| | 14 | 28 | 0000 |
| Address for primary algorithm extended query table | 15 | 2A | 0040 |
| | 16 | 2C | 0000 |
| Alternate vendor command set and control interface ID code | 17 | 2E | 0000 |
| | 18 | 30 | 0000 |
| Address for alternate algorithm extended query table | 19 | 32 | 0000 |
| | 1A | 34 | 0000 |

Table 4-2. CFI Mode: System Interface Data Values

| Description | Address (h) (Word Mode) | Address (h) (Byte Mode) | Data (h) |
|--|----------------------------|----------------------------|----------|
| Vcc supply minimum program/erase voltage | 1B | 36 | 0027 |
| Vcc supply maximum program/erase voltage | 1C | 38 | 0036 |
| VPP supply minimum program/erase voltage | 1D | 3A | 0000 |
| VPP supply maximum program/erase voltage | 1E | 3C | 0000 |
| Typical timeout per single word/byte write, 2 ⁿ us | 1F | 3E | 0004 |
| Typical timeout for maximum-size buffer write, 2 ⁿ us | 20 | 40 | 0000 |
| Typical timeout per individual block erase, 2 ⁿ ms | 21 | 42 | 000A |
| Typical timeout for full chip erase, 2 ⁿ ms | 22 | 44 | 0000 |
| Maximum timeout for word/byte write, 2 ⁿ times typical | 23 | 46 | 0005 |
| Maximum timeout for buffer write, 2 ⁿ times typical | 24 | 48 | 0000 |
| Maximum timeout per individual block erase, 2 ⁿ times typical | 25 | 4A | 0004 |
| Maximum timeout for chip erase, 2 ⁿ times typical | 26 | 4C | 0000 |

Table 4-3. CFI Mode: Device Geometry Data Values

| Description | Address (h) (Word Mode) | Address (h) (Byte Mode) | Data (h) |
|---|----------------------------|----------------------------|----------|
| Device size = 2 ⁿ in number of bytes | 27 | 4E | 0016 |
| Flash device interface description (02=asynchronous x8/x16) | 28 | 50 | 0002 |
| | 29 | 52 | 0000 |
| Maximum number of bytes in buffer write = 2 ⁿ (not support) | 2A | 54 | 0000 |
| | 2B | 56 | 0000 |
| Number of erase regions within device | 2C | 58 | 0002 |
| Index for Erase Bank Area 1 [2E,2D] = # of same-size sectors in region 1-1 [30, 2F] = sector size in multiples of 256-bytes | 2D | 5A | 0007 |
| | 2E | 5C | 0000 |
| | 2F | 5E | 0020 |
| | 30 | 60 | 0000 |
| Index for Erase Bank Area 2 | 31 | 62 | 003E |
| | 32 | 64 | 0000 |
| | 33 | 66 | 0000 |
| | 34 | 68 | 0001 |
| Index for Erase Bank Area 3 | 35 | 6A | 0000 |
| | 36 | 6C | 0000 |
| | 37 | 6E | 0000 |
| | 38 | 70 | 0000 |
| Index for Erase Bank Area 4 | 39 | 72 | 0000 |
| | 3A | 74 | 0000 |
| | 3B | 76 | 0000 |
| | 3C | 78 | 0000 |

Table 4-4. CFI Mode: Primary Vendor-Specific Extended Query Data Values

| Description | Address (h) (Word Mode) | Address (h) (Byte Mode) | Data (h) |
|---|----------------------------|----------------------------|-----------|
| Query - Primary extended table, unique ASCII string, PRI | 40 | 80 | 0050 |
| | 41 | 82 | 0052 |
| | 42 | 84 | 0049 |
| Major version number, ASCII | 43 | 86 | 0031 |
| Minor version number, ASCII | 44 | 88 | 0031 |
| Unlock recognizes address (0= recognize, 1= don't recognize) | 45 | 8A | 0000 |
| Erase suspend (2= to both read and program) | 46 | 8C | 0002 |
| Sector protect (N= # of sectors/group) | 47 | 8E | 0004 |
| Temporary sector unprotect (1=supported) | 48 | 90 | 0001 |
| Sector protect/Chip unprotect scheme | 49 | 92 | 0004 |
| Simultaneous R/W operation (0=not supported) | 4A | 94 | 0000 |
| Burst mode (0=not supported) | 4B | 96 | 0000 |
| Page mode (0=not supported) | 4C | 98 | 0000 |
| Minimum ACC (acceleration) supply (0= not supported), [D7:D4] for volt, [D3:D0] for 100mV | 4D | 9A | 0095 |
| Maximum ACC (acceleration) supply (0= not supported), [D7:D4] for volt, [D3:D0] for 100mV | 4E | 9C | 00A5 |
| Top/Bottom boot block indicator 02h=bottom boot device 03h=top boot device | 4F | 9E | 0002/0003 |

ELECTRICAL CHARACTERISTICS**ABSOLUTE MAXIMUM STRESS RATINGS**

| | | |
|---|--------------------|--------------------|
| Surrounding Temperature with Bias | | -65°C to +125°C |
| Storage Temperature | | -65°C to +150°C |
| Voltage Range | VCC | -0.5V to +4.0 V |
| | RESET#, A9 and OE# | -0.5V to +10.5 V |
| | The other pins | -0.5V to Vcc +0.5V |
| Output Short Circuit Current (less than one second) | | 200 mA |

Note:

1. Minimum voltage may undershoot to -2V during transition and for less than 20ns during transitions.
2. Maximum voltage may overshoot to Vcc+2V during transition and for less than 20ns during transitions.

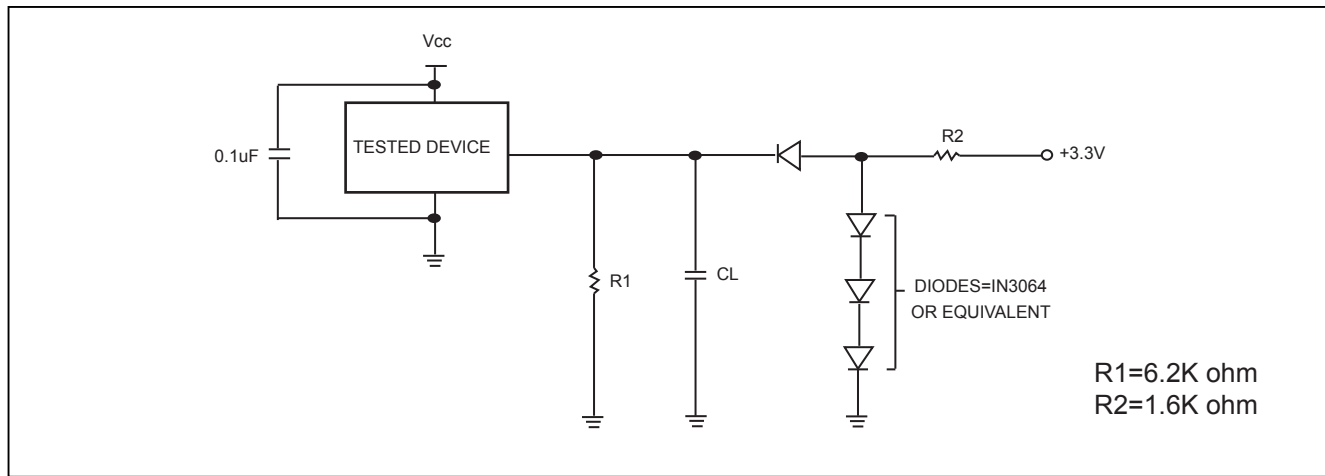
OPERATING TEMPERATURE AND VOLTAGE

| | | |
|-----------------------------|------------------------------|-----------------|
| Industrial (I) Grade | Surrounding Temperature (TA) | -40°C to +85°C |
| VCC Supply Voltages | VCC range | +2.7 V to 3.6 V |

DC CHARACTERISTICS

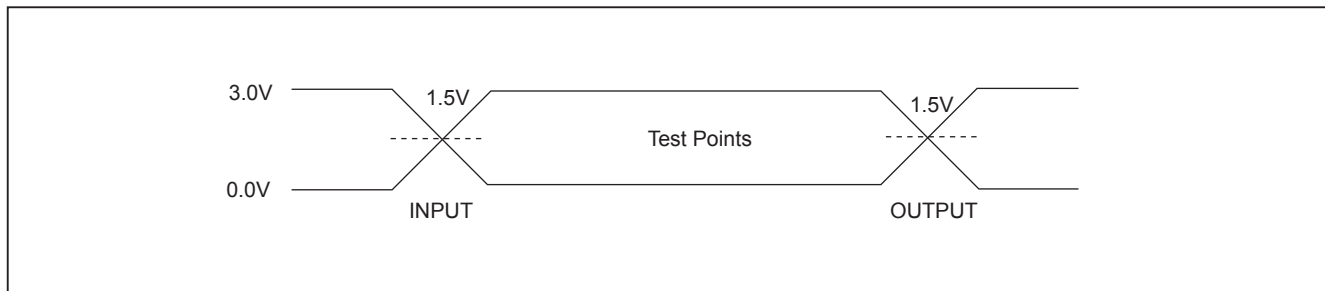
| Symbol | Description | Min. | Typ. | Max. | Remark |
|-------------------|---|-----------------------|------|---------------------------------|--|
| Iilk | Input Leak | | | ± 1.0uA | |
| Iilk9 | A9 Leak | | | 35uA(0~70°C)/ 45uA(-40~85°C) | A9=10.5V |
| Iolk | Output Leak | | | ± 1.0uA | |
| Icr1 | Read Current(5MHz) | | 10mA | 16mA | CE#=Vil, OE#=Vih |
| Icr2 | Read Current(1MHz) | | 2mA | 4mA | CE#=Vil, OE#=Vih |
| Icw | Write Current | | 15mA | 30mA | CE#=Vil, OE#=Vih, WE#=Vil |
| I _{sb} | Standby Current | | 5uA | 15uA | V _{cc} =V _{cc} max, other pin disable |
| I _{sr} | Reset Current | | 5uA | 15uA | V _{cc} =V _{cc} max, Reset# enable, other pin disable |
| I _{sb} s | Sleep Mode Current | | 5uA | 15uA | |
| Icp1 | Accelerated Pgm Current, WP#/Acc pin (Word/Byte) | | 5mA | 10mA | CE#=Vil, OE#=Vih |
| Icp2 | Accelerated Pgm Current, Vcc pin, (Word/Byte) | | 15mA | 30mA | CE#=Vil, OE#=Vih |
| Vil | Input Low Voltage | -0.5V | | 0.8V | |
| Vih | Input High Voltage | 0.7xV _{cc} | | V _{cc} +0.3V | |
| V _{hv} | Very High Voltage for hardware Protect/Unprotect/Accelerated Program/Auto Select/Temporary Unprotect | 9.5V | | 10.5V | |
| V _{ol} | Output Low Voltage | | | 0.45V | I _{ol} =4.0mA |
| V _{oh1} | Output High Voltage | 0.85xV _{cc} | | | I _{oh1} =-2mA |
| V _{oh2} | Output High Voltage | V _{cc} -0.4V | | | I _{oh2} =-100uA |
| V _{lko} | Low Vcc Lock-out Voltage | 2.3V | | 2.5V | |

SWITCHING TEST CIRCUIT



Test Condition
 Output Load : 1 TTL gate
 Output Load Capacitance, CL : 30pF
 Rise/Fall Times : 5ns
 In/Out reference levels : 1.5V

SWITCHING TEST WAVEFORM



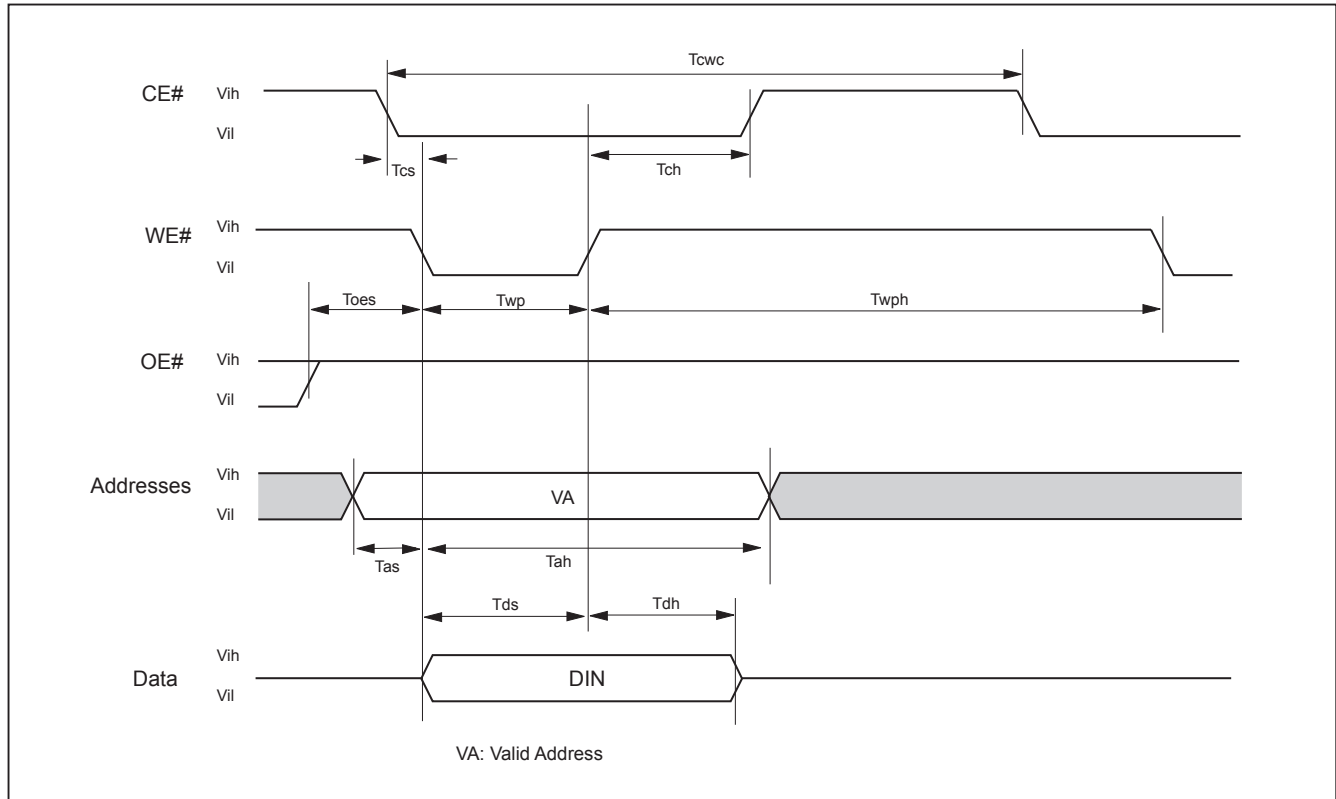
AC CHARACTERISTICS

| Symbol | Description | Min. | Typ. | Max. | Unit | |
|--------|---|---------------------------|------|------|------|----|
| Taa | Valid data output after address | | | 70 | ns | |
| Tce | Valid data output after CE# low | | | 70 | ns | |
| Toe | Valid data output after OE# low | | | 30 | ns | |
| Tdf | Data output floating after OE# high | | | 30 | ns | |
| Toh | Output hold time from the earliest rising edge of address, CE#, OE# | 0 | | | ns | |
| Trc | Read period time | 70 | | | ns | |
| Tsrw | Latency Between Read and Write Operation (*Note 1) | 45 | | | ns | |
| Twc | Write period time | 70 | | | ns | |
| Tcwc | Command write period time | 70 | | | ns | |
| Tas | Address setup time | 0 | | | ns | |
| Tah | Address hold time | 45 | | | ns | |
| Tds | Data setup time | 45 | | | ns | |
| Tdh | Data hold time | 0 | | | ns | |
| Tvcs | Vcc setup time | 200 | | | us | |
| Tcs | Chip enable Setup time | 0 | | | ns | |
| Tch | Chip enable hold time | 0 | | | ns | |
| Toes | Output enable setup time | 0 | | | ns | |
| Toeh | Output enable hold time | Read | 0 | | ns | |
| | | Toggle & Data# Polling | | | | |
| Tws | WE# setup time | 0 | | | ns | |
| Twh | WE# hold time | 0 | | | ns | |
| Tcep | CE# pulse width | 45 | | | ns | |
| Tceph | CE# pulse width high | 30 | | | ns | |
| Twp | WE# pulse width | 35 | | | ns | |
| Twph | WE# pulse width high | 30 | | | ns | |
| Tbusy | Program/Erase active time by RY/BY# | | | 90 | ns | |
| Tghwl | Read recover time before write | 0 | | | ns | |
| Tghel | Read recover time before write | 0 | | | ns | |
| Twhwh1 | Program operation | Byte | | 9 | 300 | us |
| | | Word | | 11 | 360 | us |
| Twhwh1 | Acc program operation (Word/Byte) | | 7 | 210 | us | |
| Twhwh2 | Sector erase operation | | 0.7 | 2 | sec | |
| Tbal | Sector add hold time | | 35 | 50 | us | |

* Note 1: Sampled only, not 100% tested.

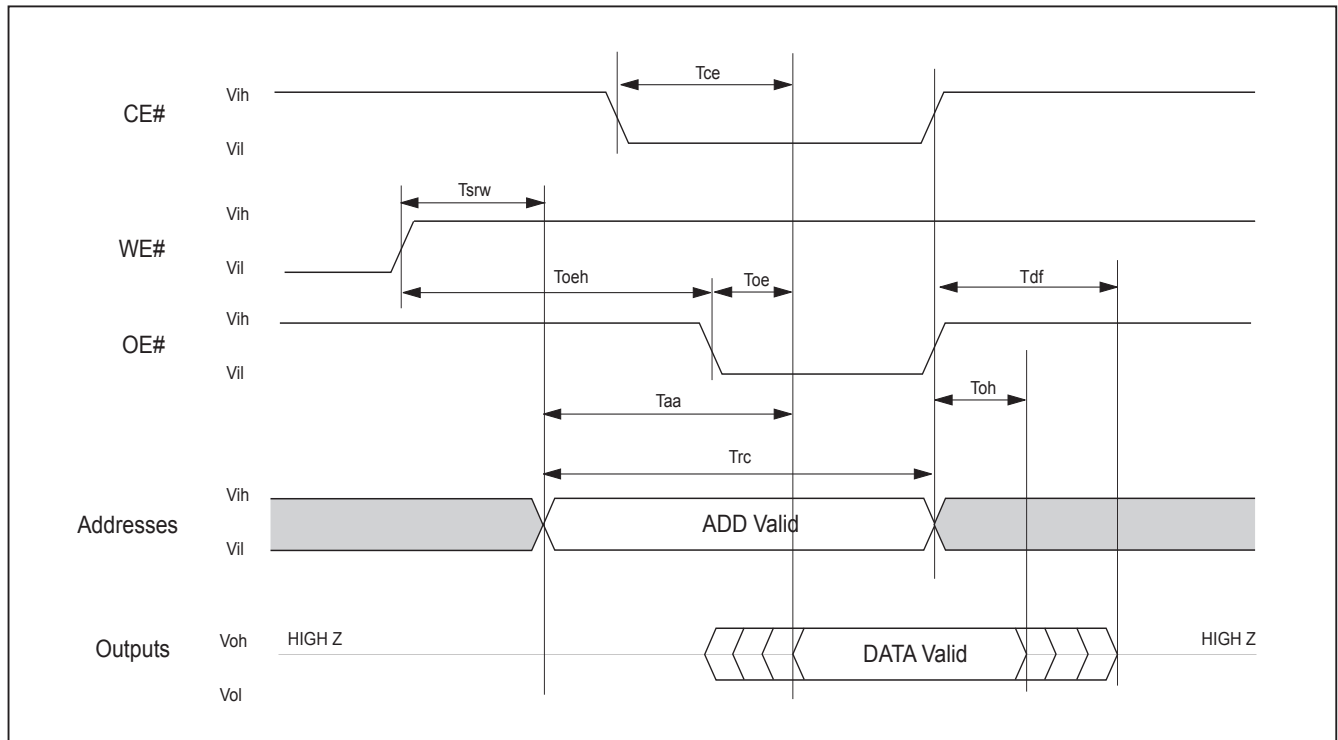
WRITE COMMAND OPERATION

Figure 1. COMMAND WRITE OPERATION



READ/RESET OPERATION

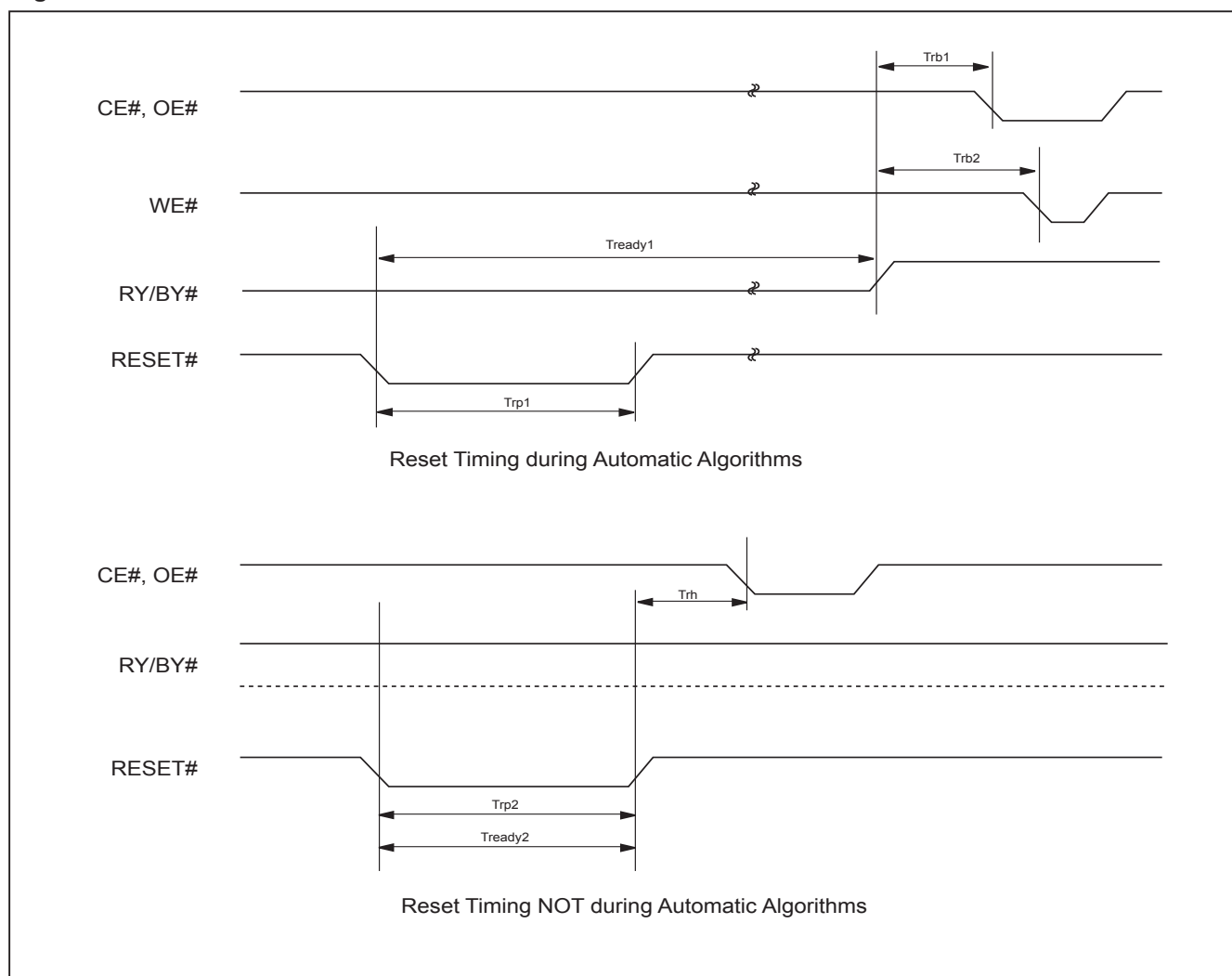
Figure 2. READ TIMING WAVEFORM



AC CHARACTERISTICS

| Item | Description | Setup | Speed | Unit |
|---------|---|-------|-------|------|
| Trp1 | RESET# Pulse Width (During Automatic Algorithms) | MIN | 10 | us |
| Trp2 | RESET# Pulse Width (NOT During Automatic Algorithms) | MIN | 500 | ns |
| Trh | RESET# High Time Before Read | MIN | 70 | ns |
| Trb1 | RY/BY# Recovery Time (to CE#, OE# go low) | MIN | 0 | ns |
| Trb2 | RY/BY# Recovery Time (to WE# go low) | MIN | 50 | ns |
| Tready1 | RESET# PIN Low (During Automatic Algorithms) to Read or Write | MAX | 20 | us |
| Tready2 | RESET# PIN Low (NOT During Automatic Algorithms) to Read or Write | MAX | 500 | ns |

Figure 3. RESET# TIMING WAVEFORM



ERASE/PROGRAM OPERATION

Figure 4. AUTOMATIC CHIP ERASE TIMING WAVEFORM

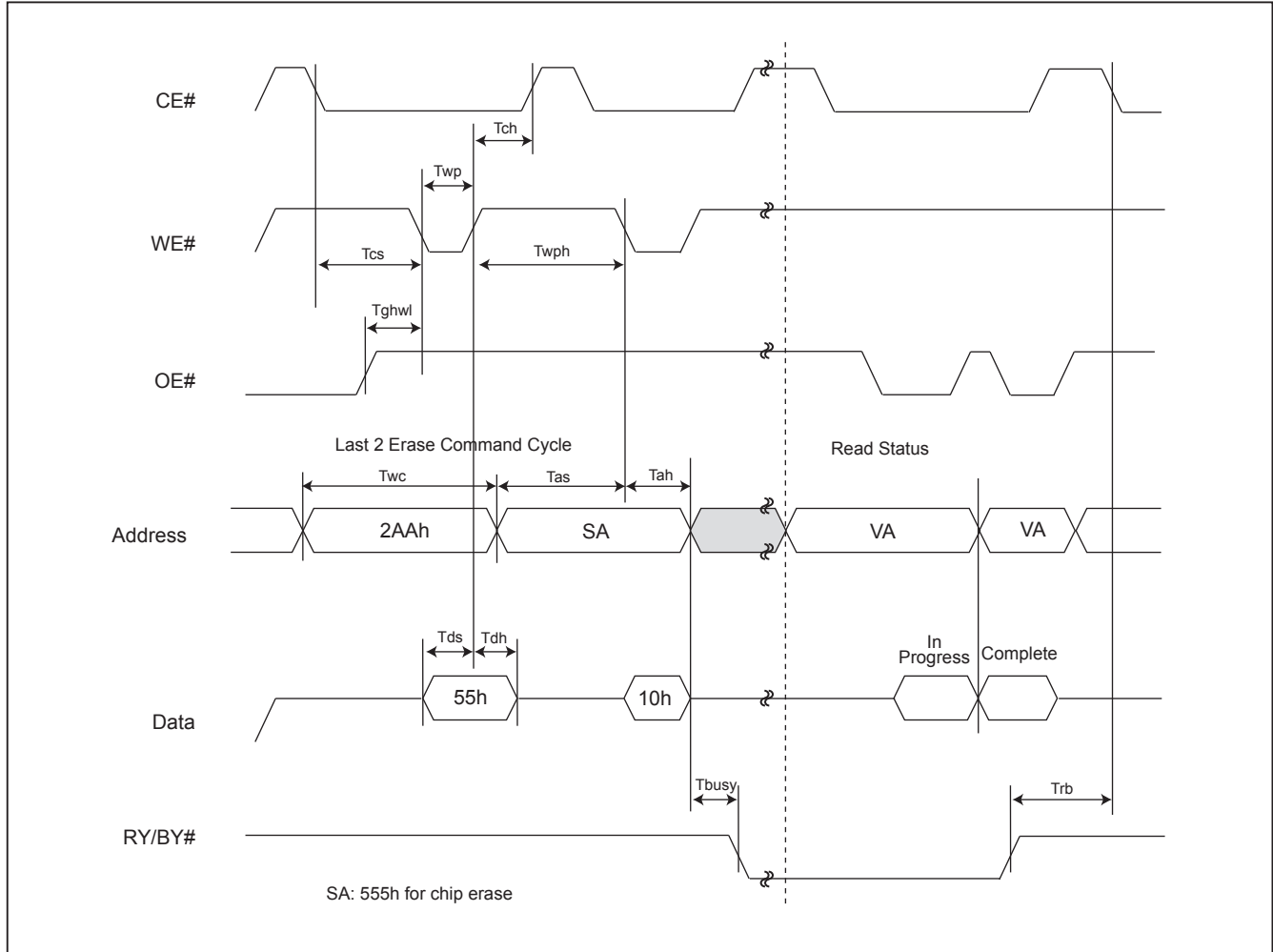


Figure 5. AUTOMATIC CHIP ERASE ALGORITHM FLOWCHART

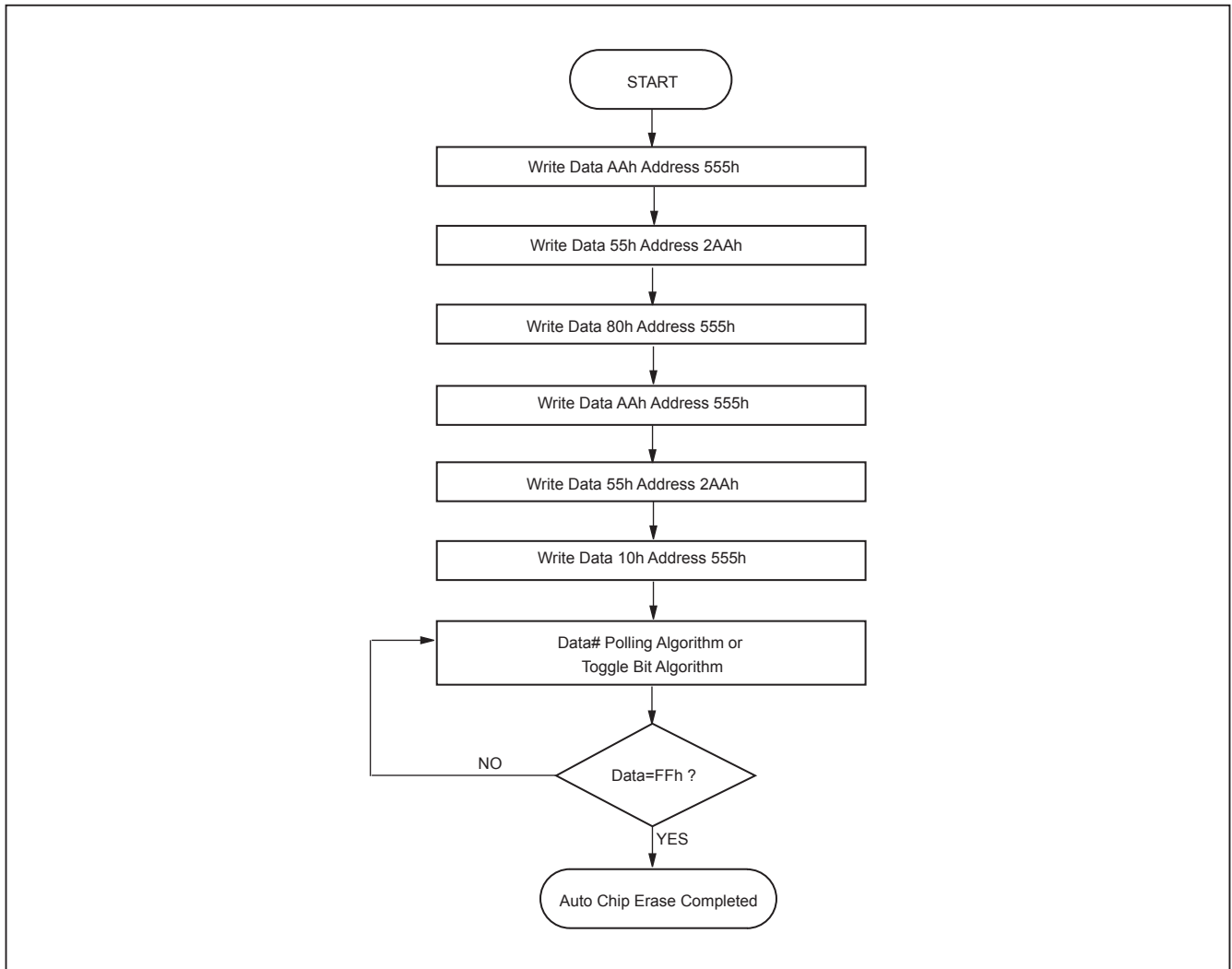


Figure 6. AUTOMATIC SECTOR ERASE TIMING WAVEFORM

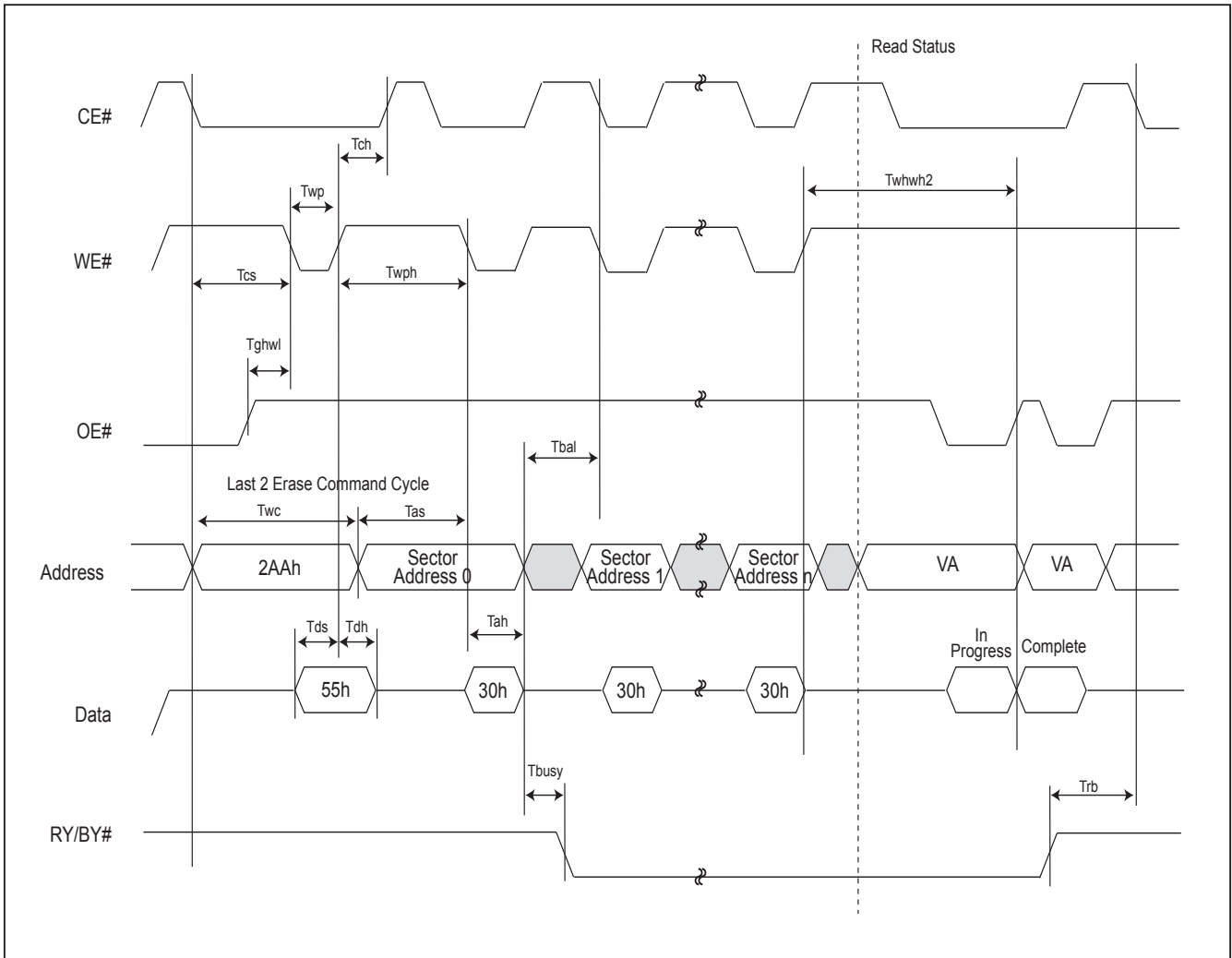


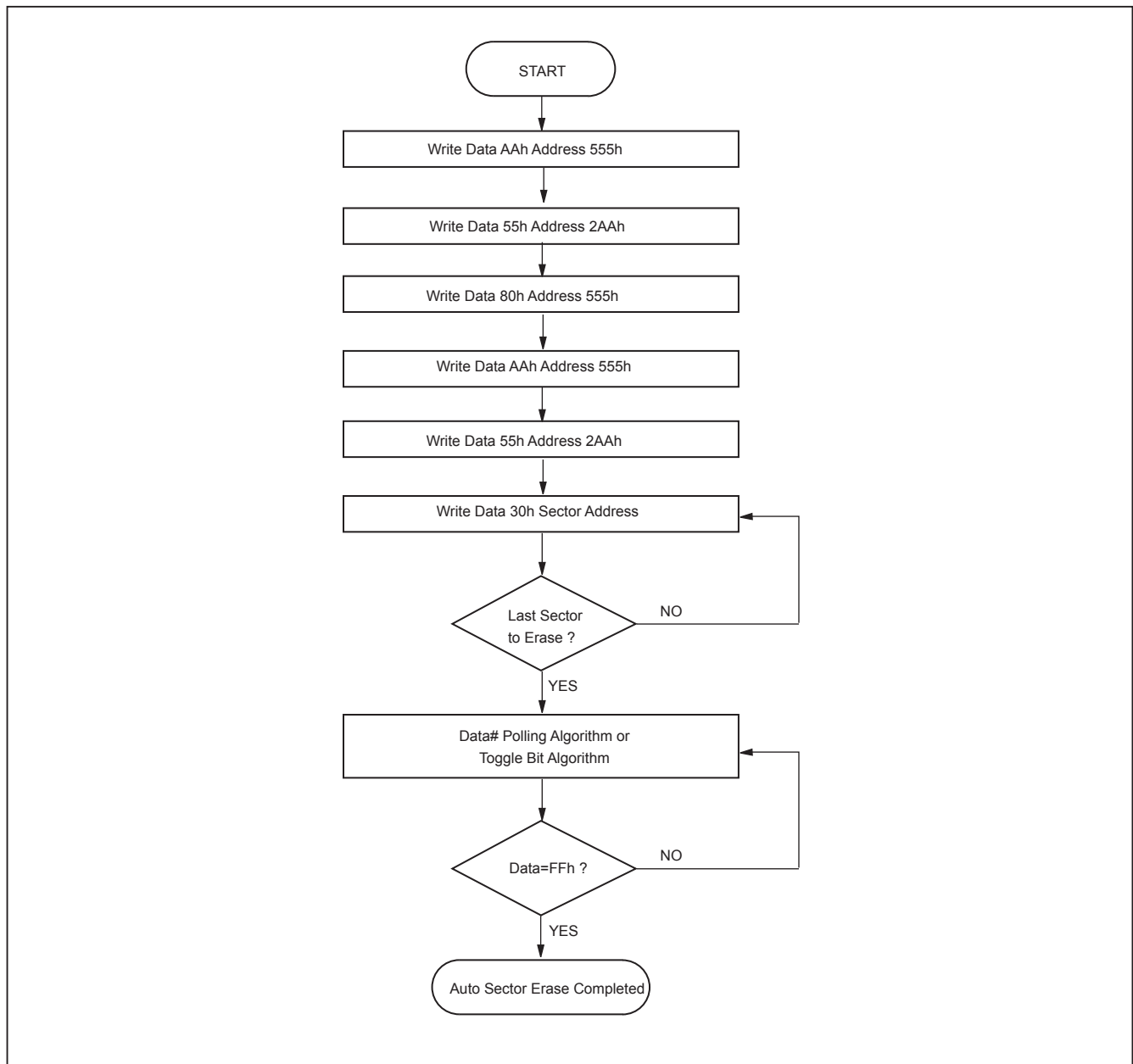
Figure 7. AUTOMATIC SECTOR ERASE ALGORITHM FLOWCHART

Figure 8. ERASE SUSPEND/RESUME FLOWCHART

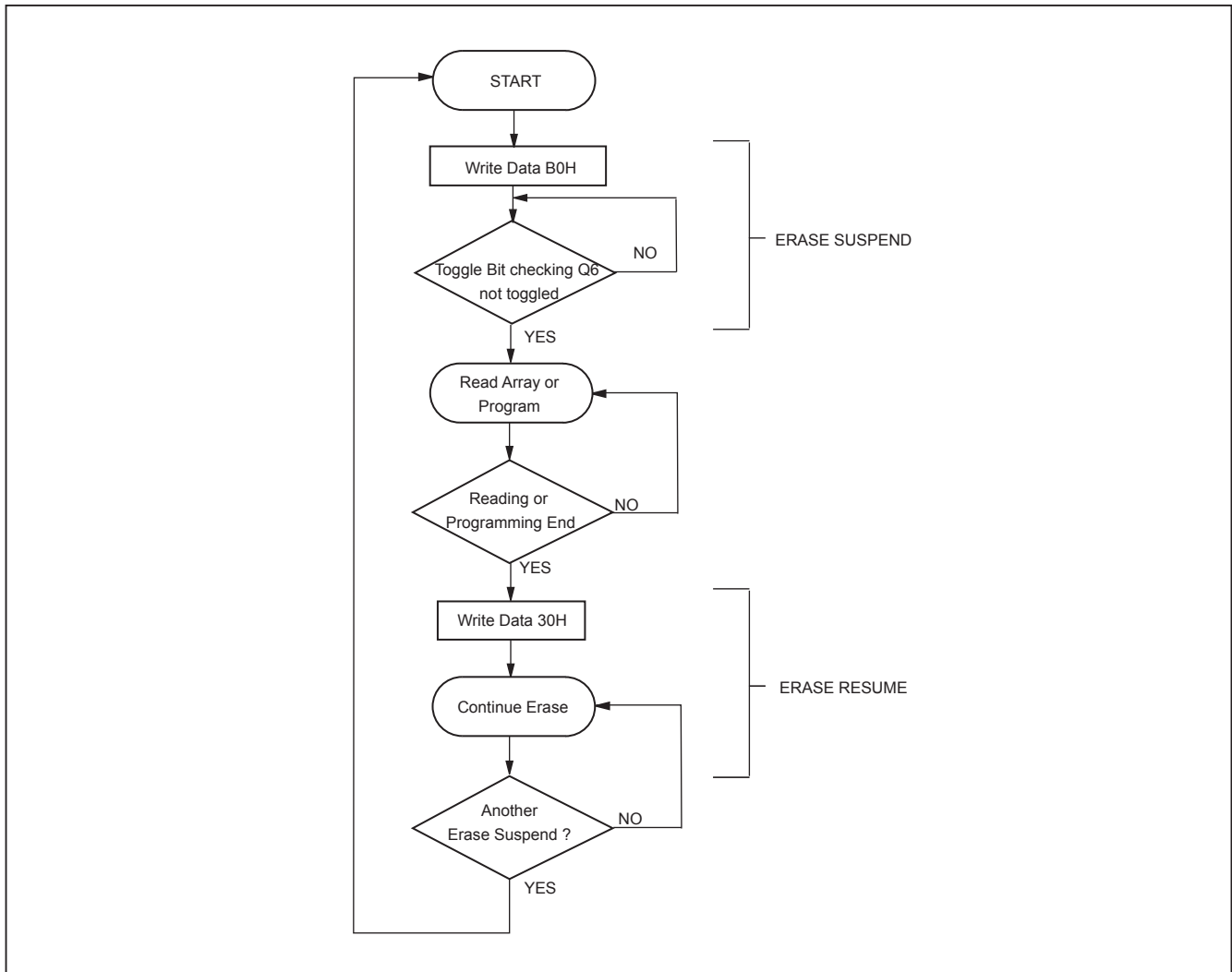


Figure 9. AUTOMATIC PROGRAM TIMING WAVEFORM

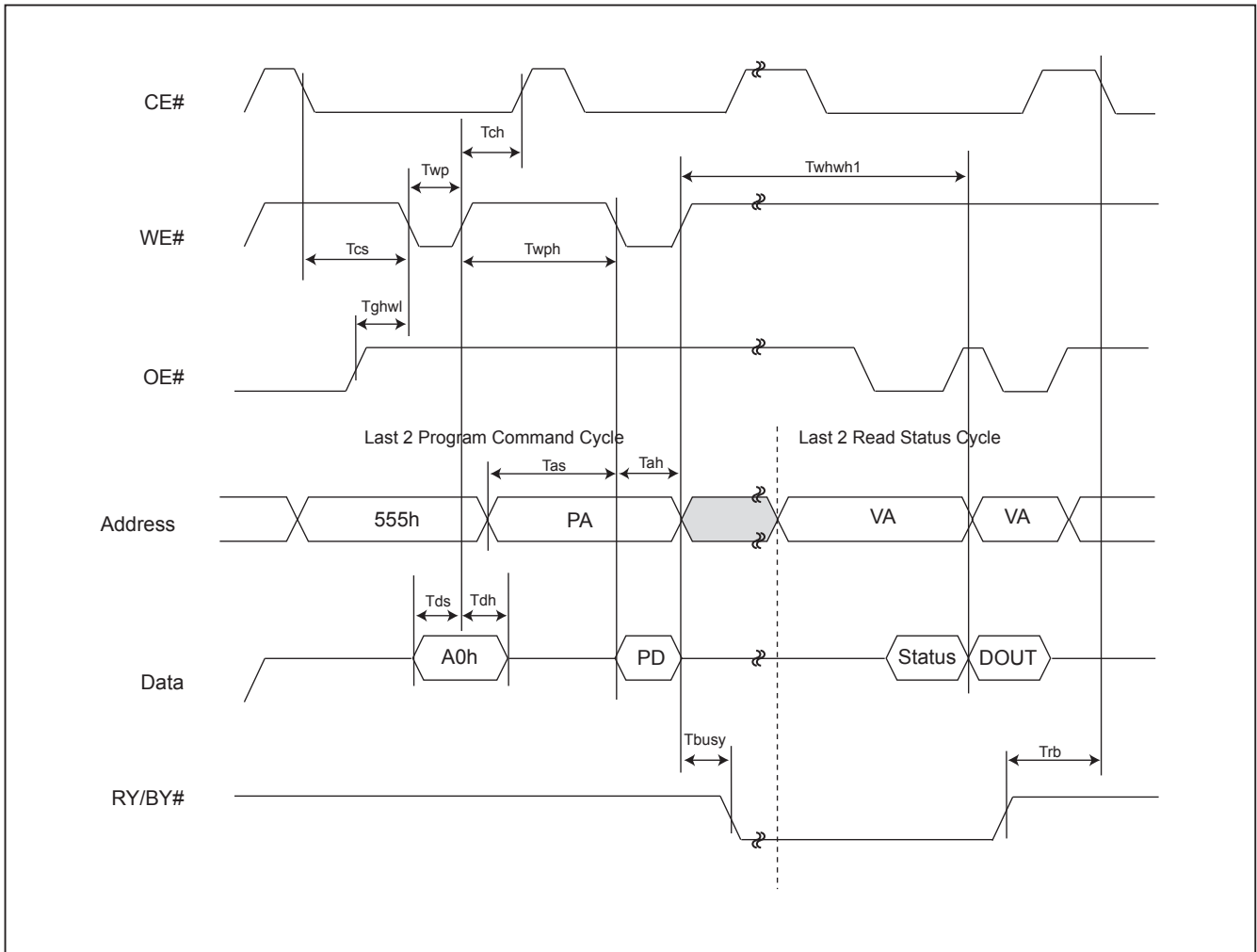


Figure 10. ACCELERATED PROGRAM TIMING DIAGRAM

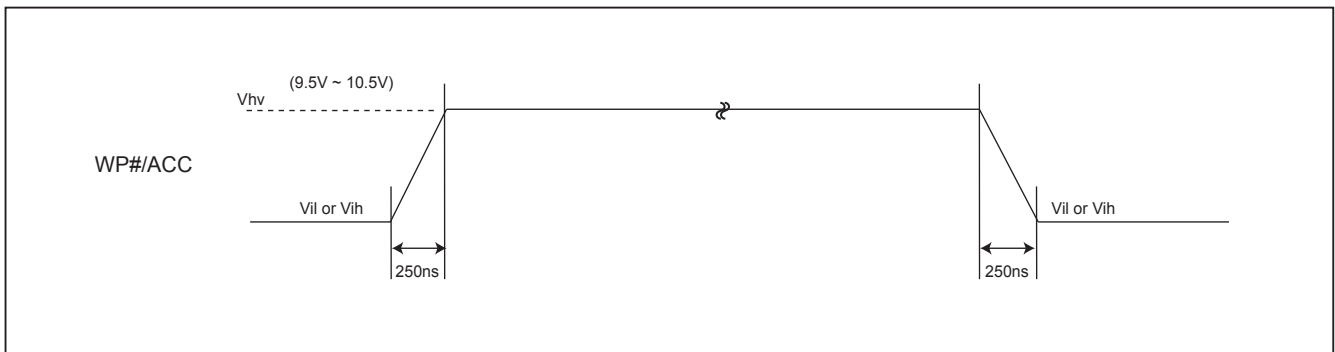


Figure 11. CE# CONTROLLED WRITE TIMING WAVEFORM

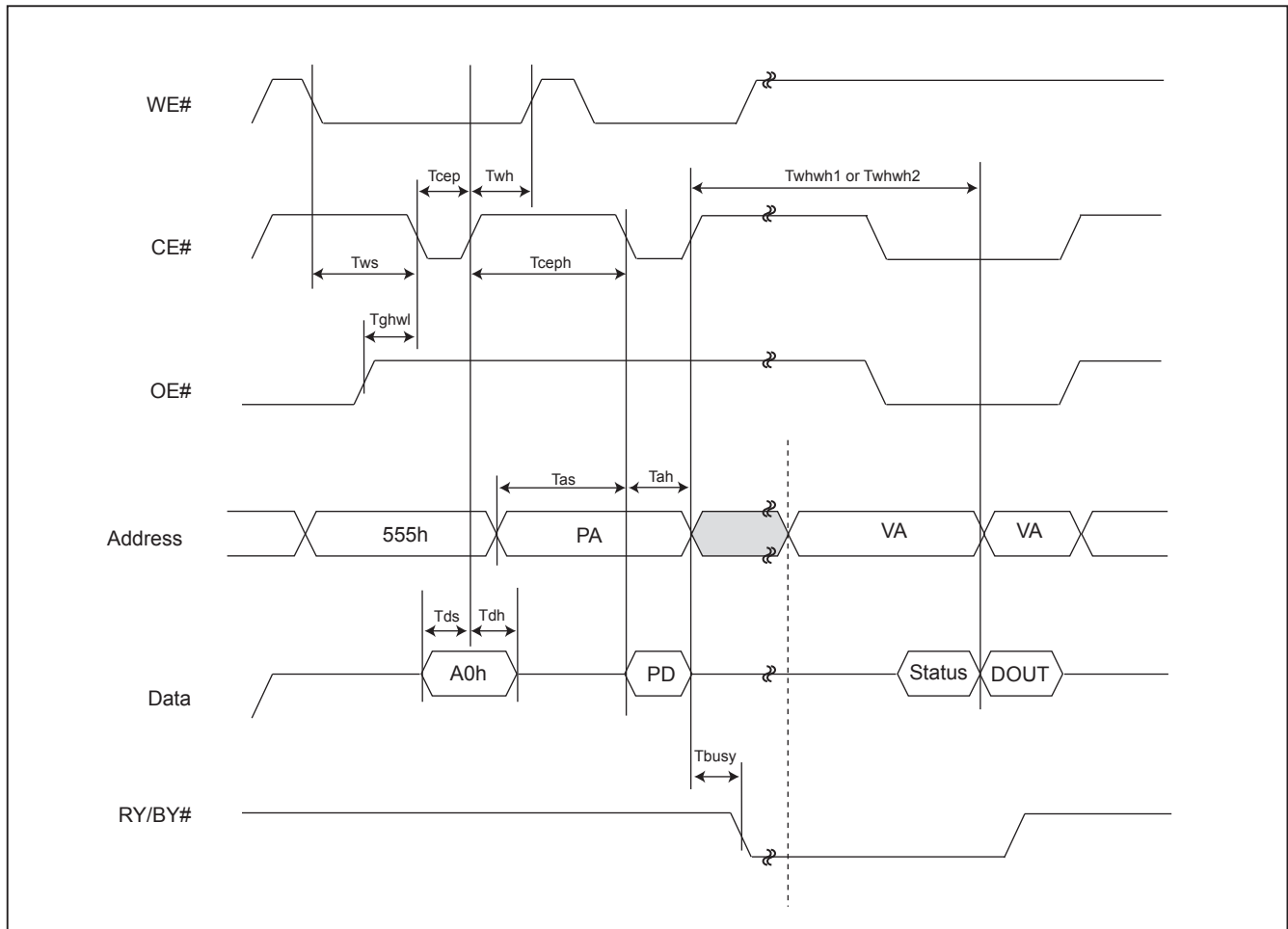
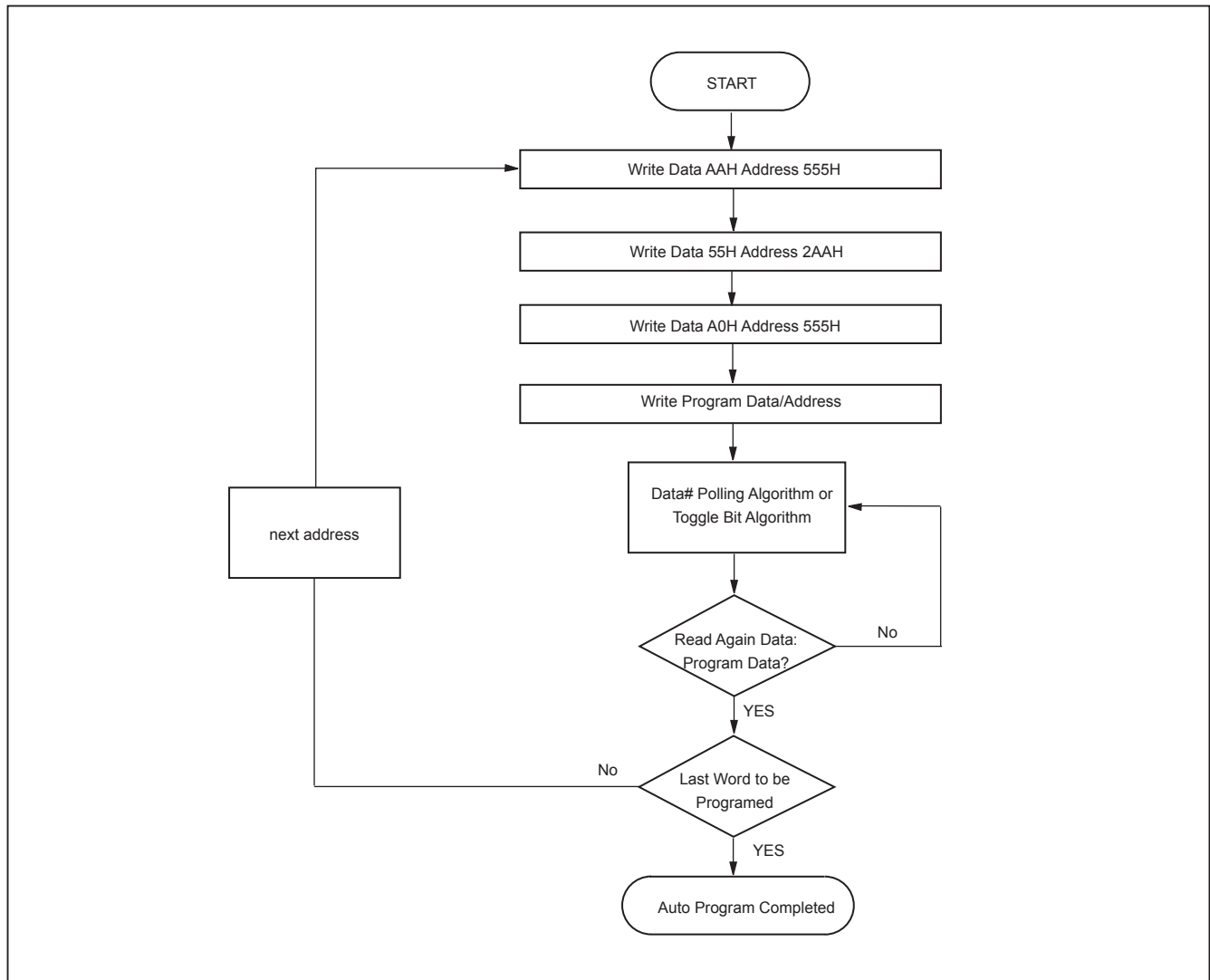


Figure 12. AUTOMATIC PROGRAMMING ALGORITHM FLOWCHART



SECTOR GROUP PROTECT/CHIP UNPROTECT

Figure 13. SECTOR GROUP PROTECT/CHIP UNPROTECT WAVEFORM (RESET# Control)

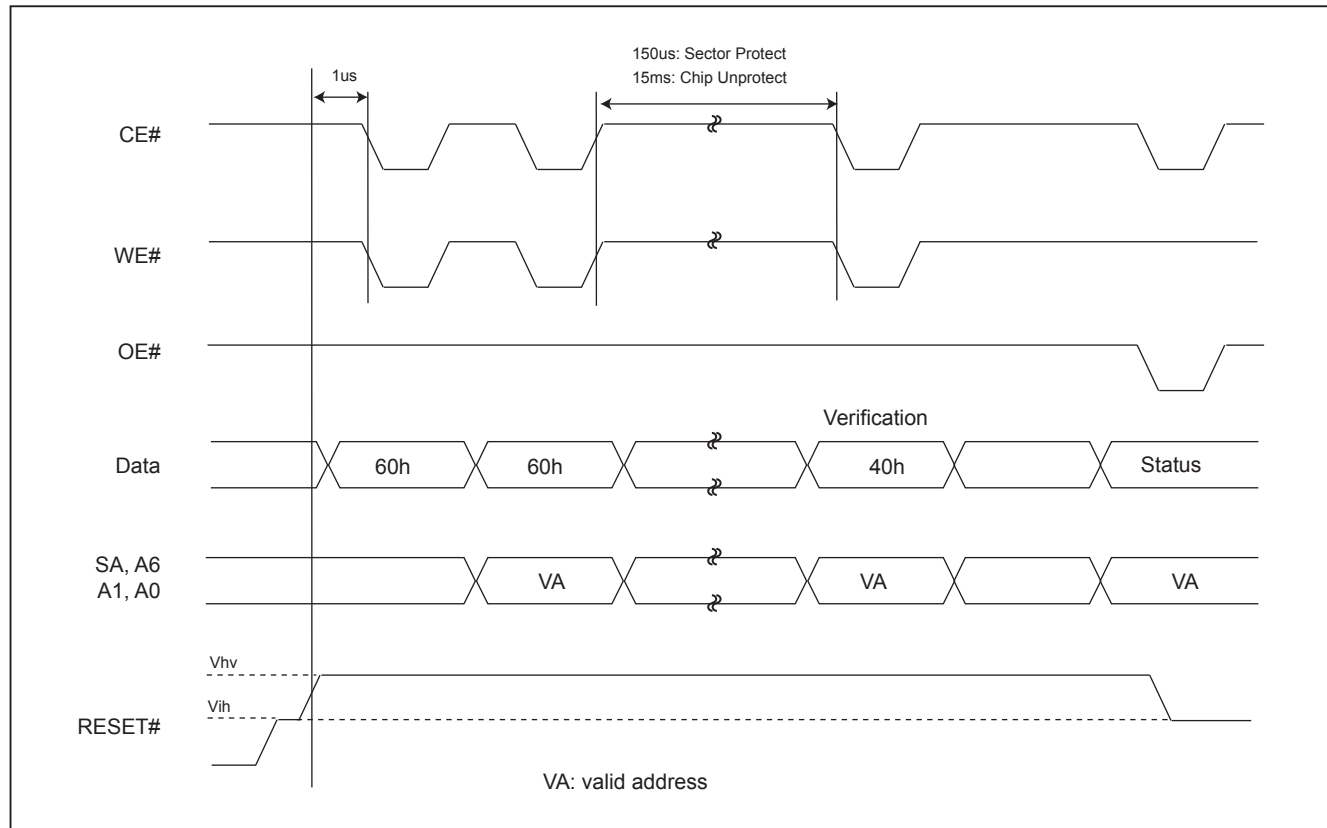


Figure 14. IN-SYSTEM SECTOR GROUP PROTECT WITH RESET#=Vhv

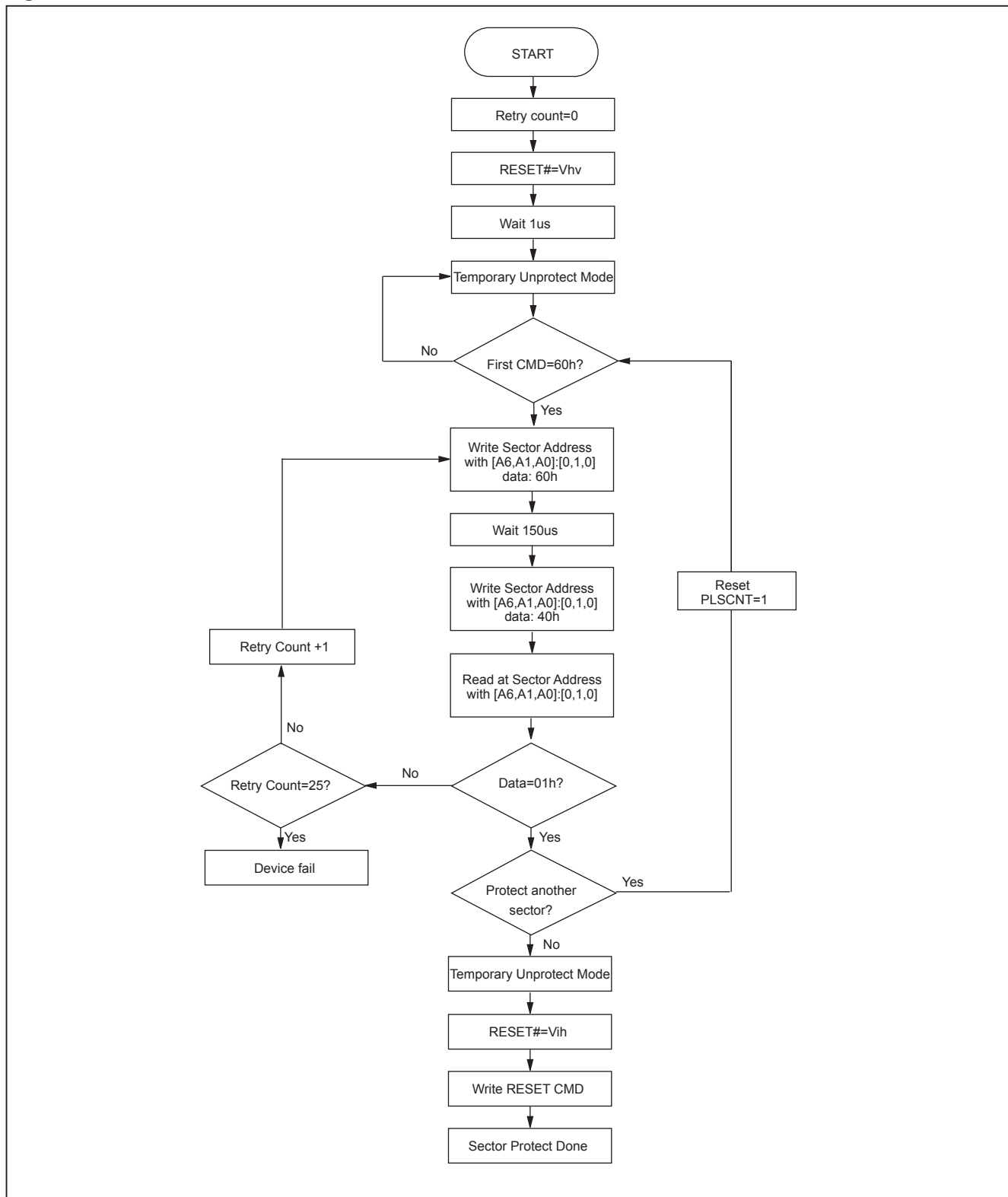


Figure 15. CHIP UNPROTECT ALGORITHM WITH RESET#=Vhv

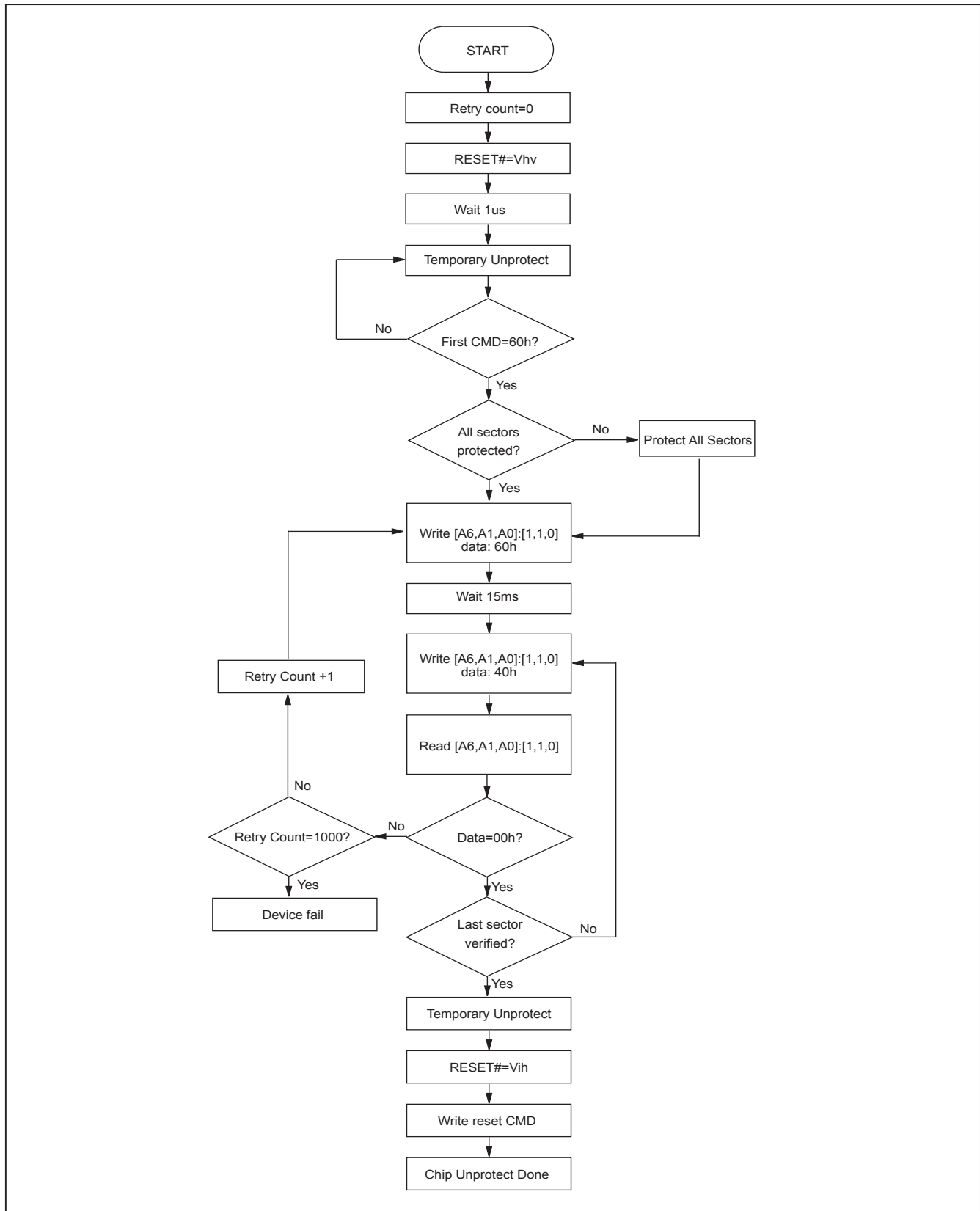


Table 5. TEMPORARY SECTOR GROUP UNPROTECT

| Parameter | Alt | Description | Condition | Speed | Unit |
|-----------|-------|---|-----------|-------|------|
| Trpvhh | Tvidr | RESET# Rise Time to Vhv and Vhv Fall Time to RESET# | MIN | 500 | ns |
| Tvhhl | Trsp | RESET# Vhv to WE# Low | MIN | 4 | us |

Figure 16. TEMPORARY SECTOR GROUP UNPROTECT WAVEFORM

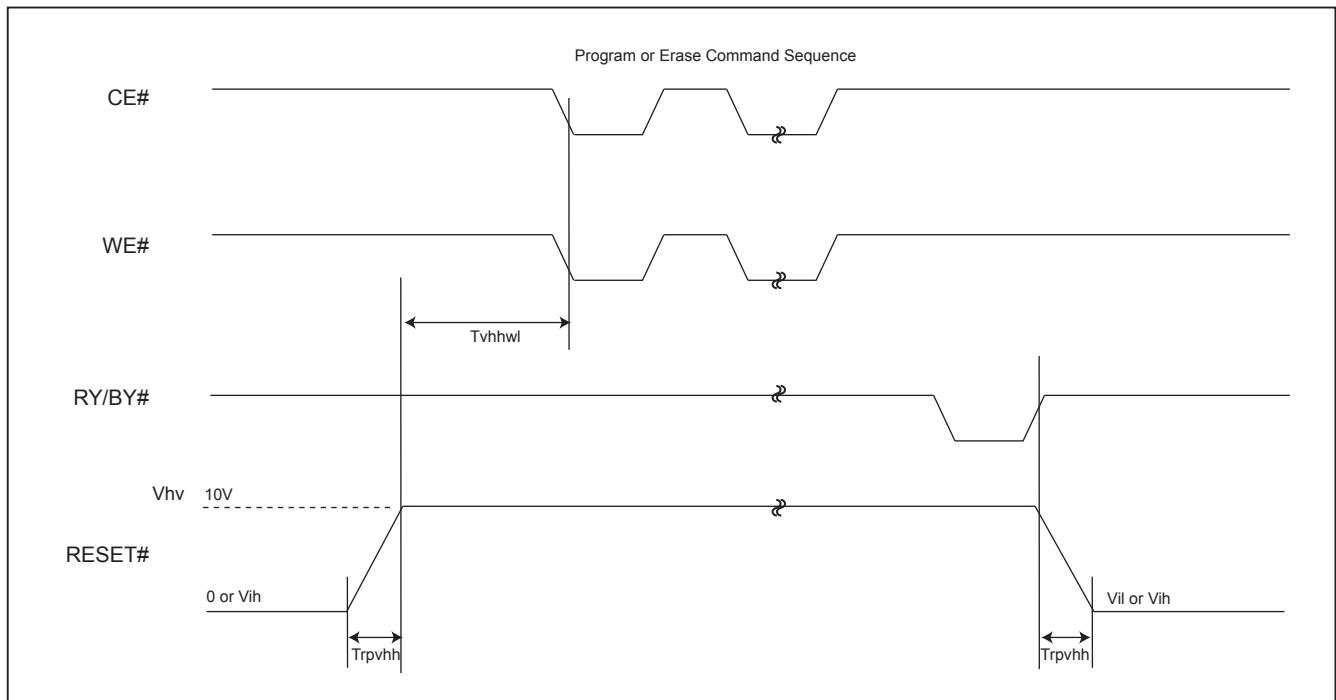
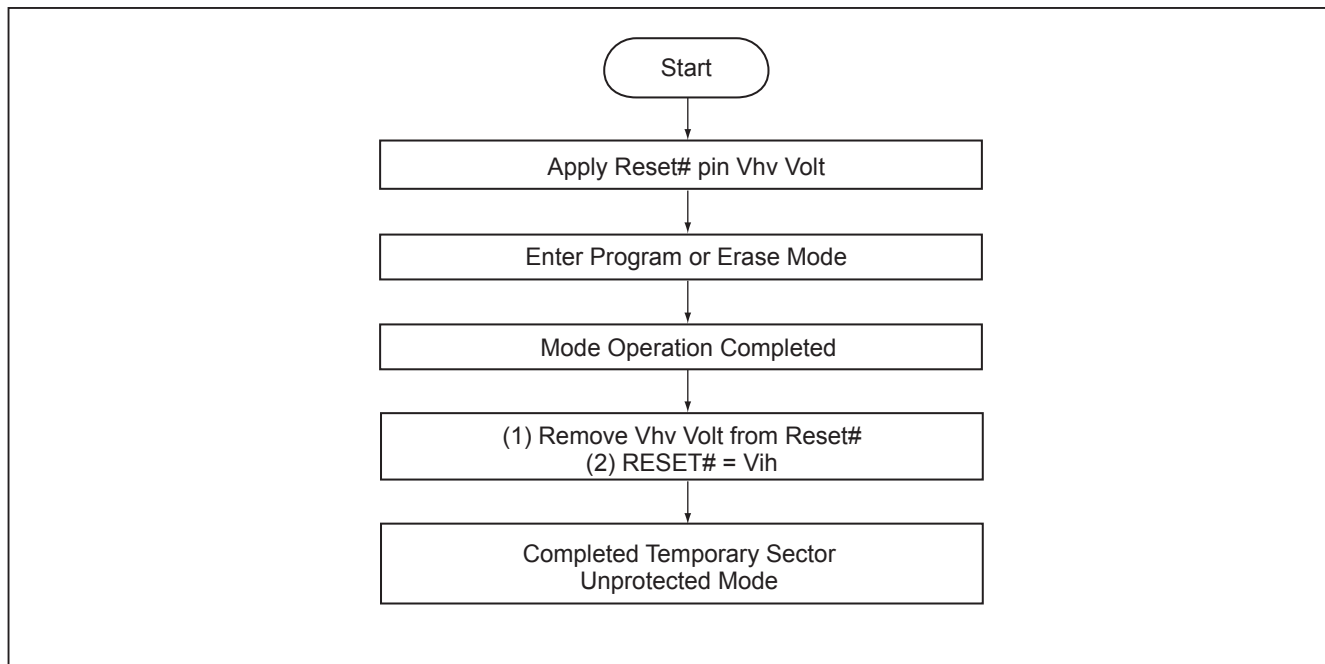
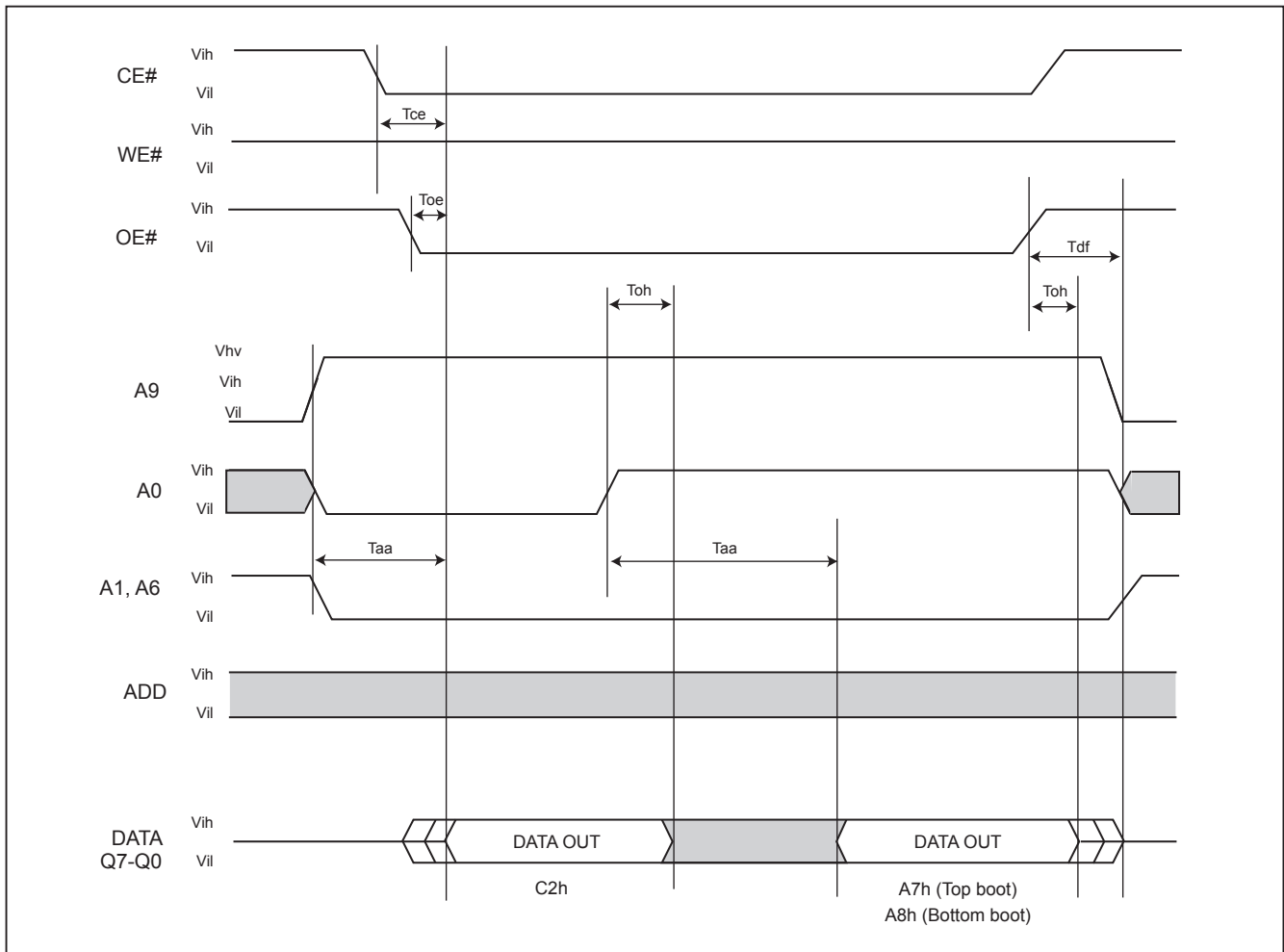


Figure 17. TEMPORARY SECTOR GROUP UNPROTECT FLOWCHART**Notes:**

1. Temporary unprotect all protected sectors Vhv=9.5~10.5V.
2. After leaving temporary unprotect mode, the previously protected sectors are again protected.

Figure 18. SILICON ID READ TIMING WAVEFORM



WRITE OPERATION STATUS

Figure 19. DATA# POLLING TIMING WAVEFORM (DURING AUTOMATIC ALGORITHM)

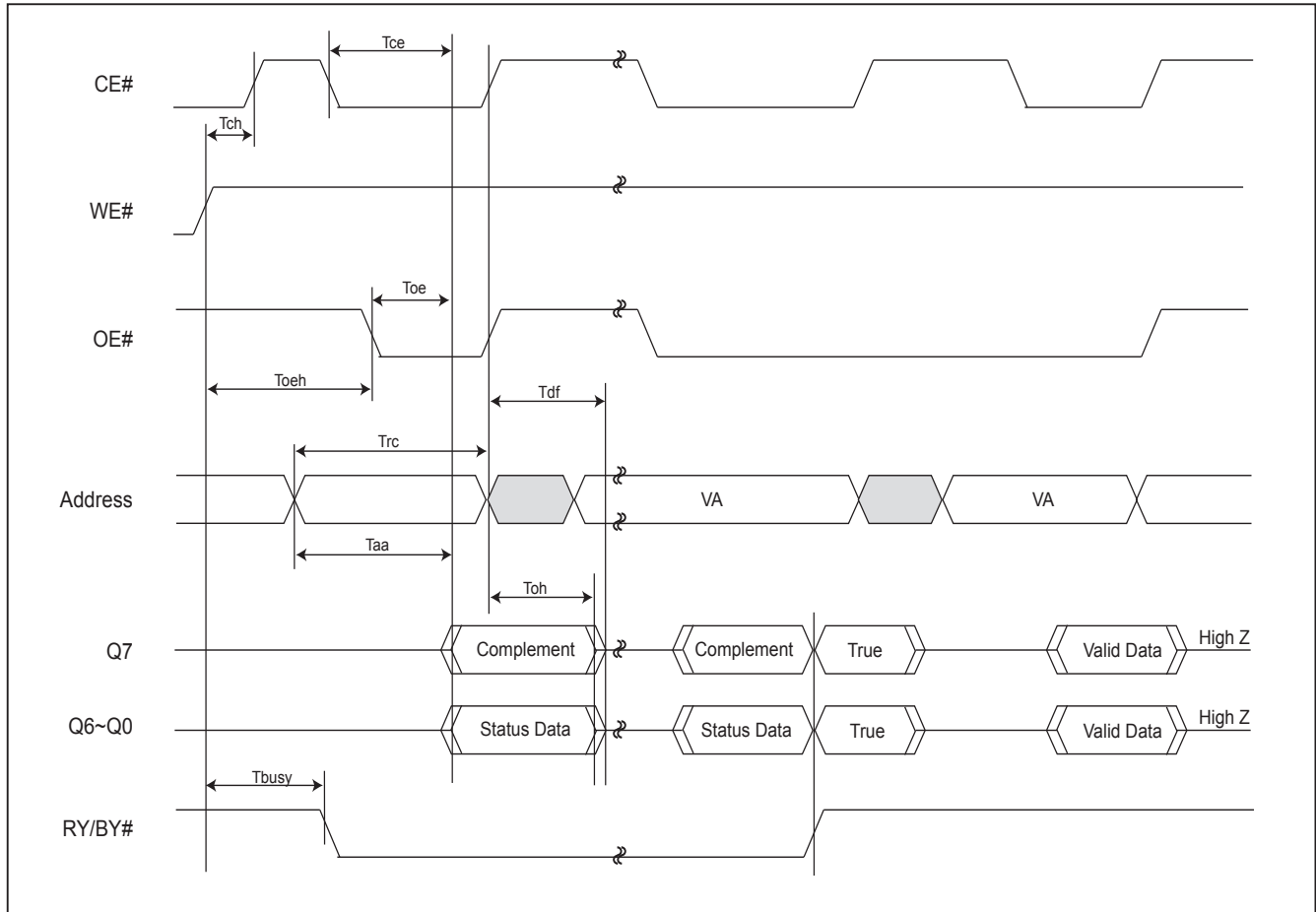
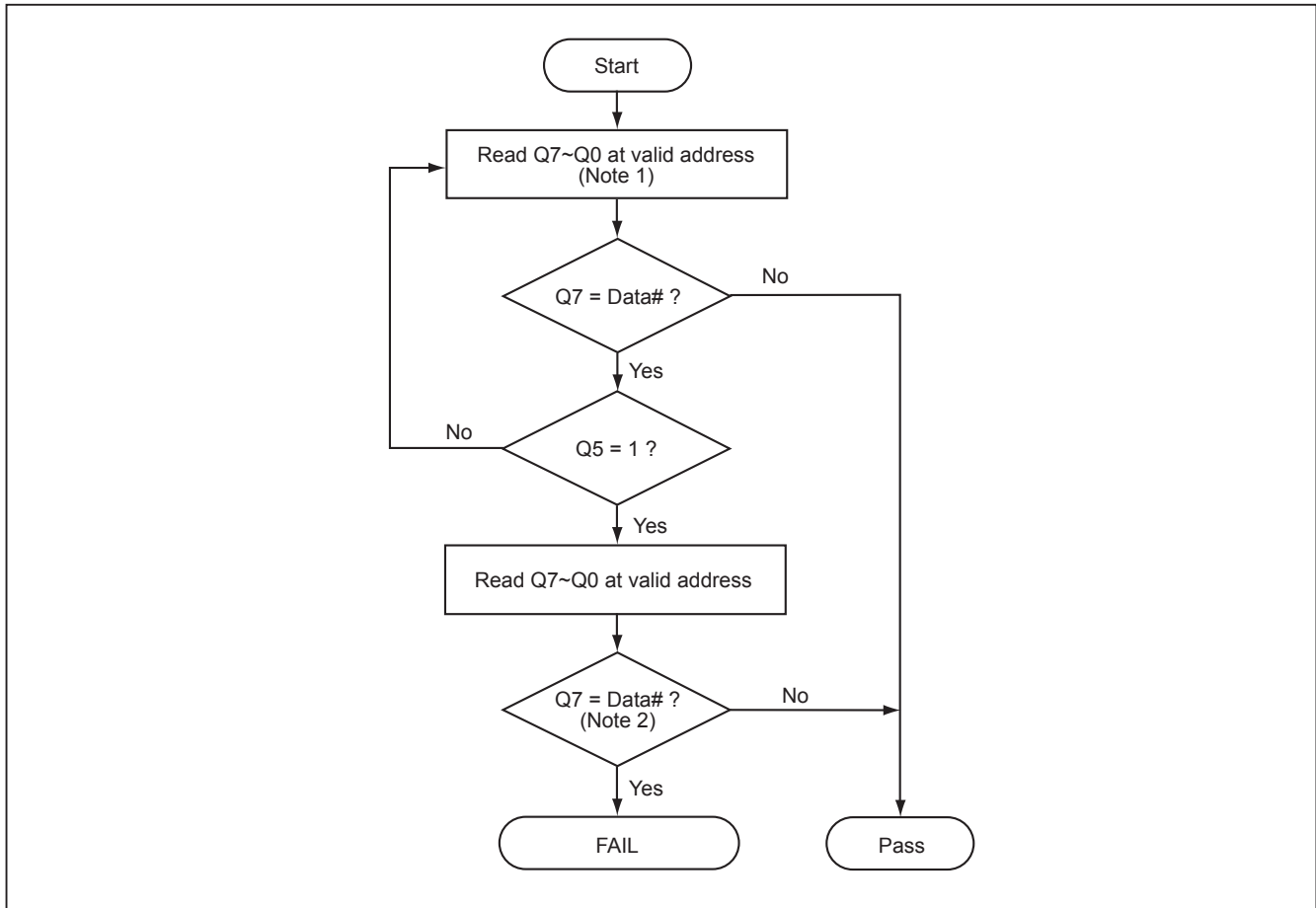


Figure 20. DATA# POLLING ALGORITHM**Notes:**

1. For programming, valid address means program address.
For erasing, valid address means erase sectors address.
2. Q7 should be rechecked even Q5="1" because Q7 may change simultaneously with Q5.

Figure 21. TOGGLE BIT TIMING WAVEFORM (DURING AUTOMATIC ALGORITHM)

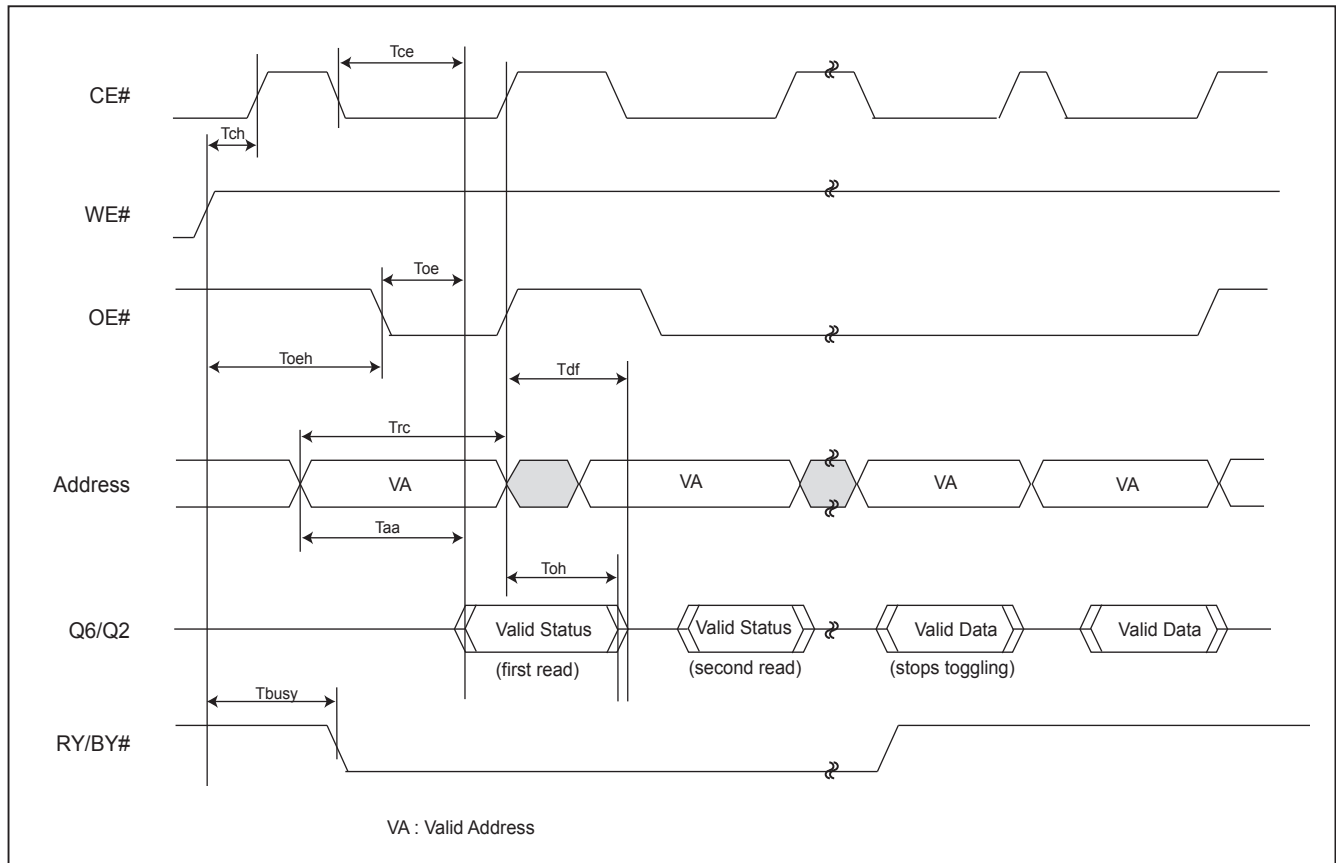
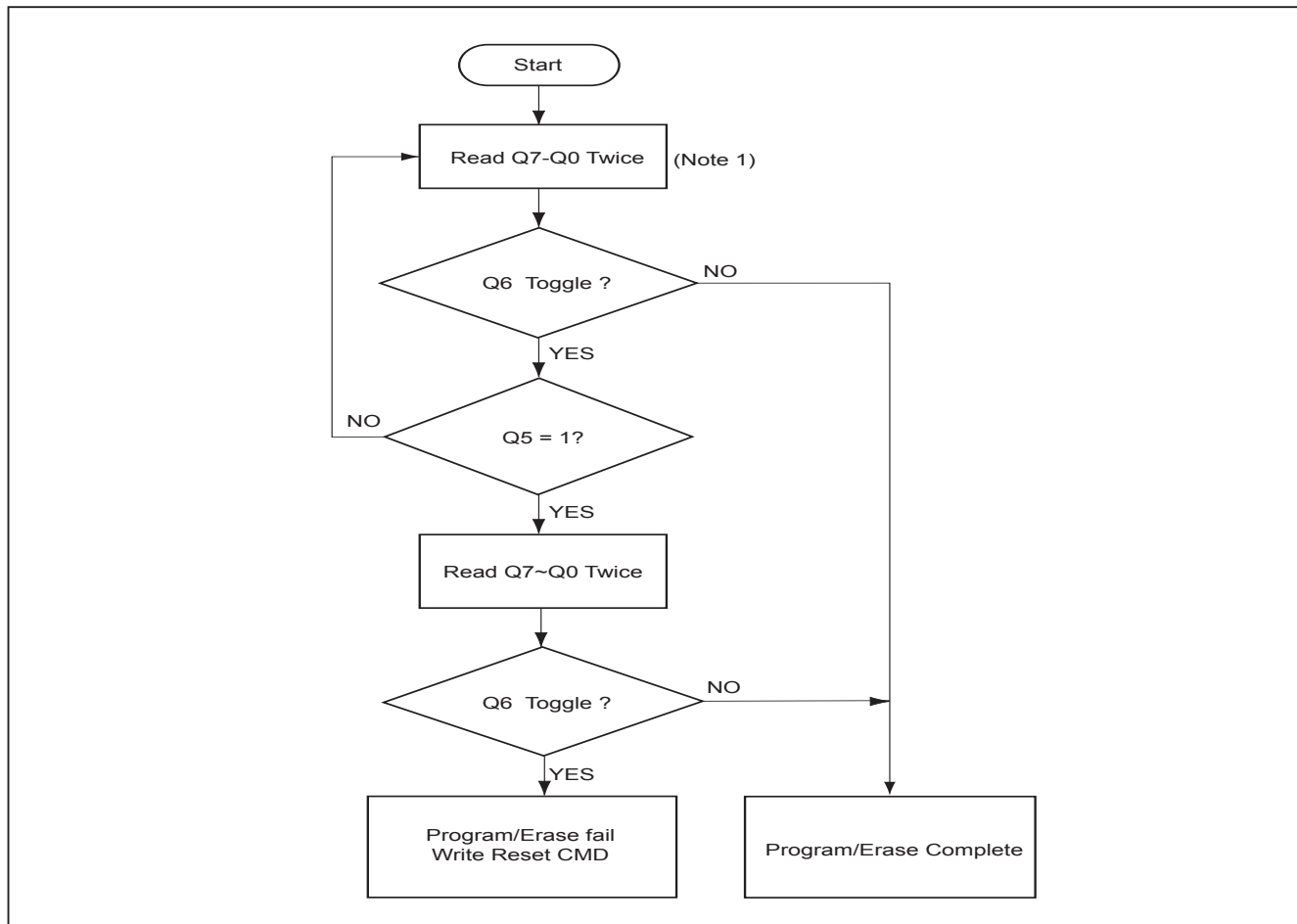


Figure 22. TOGGLE BIT ALGORITHM



Notes:

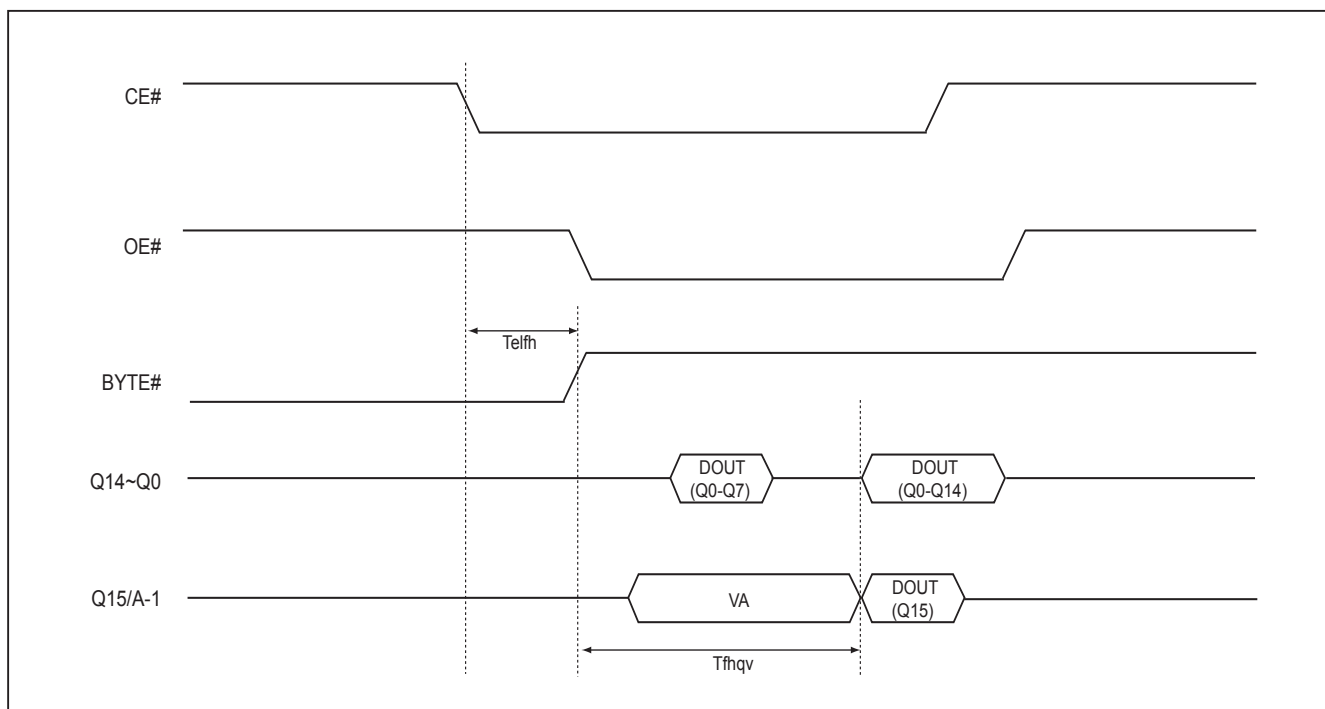
1. Read toggle bit twice to determine whether or not it is toggling.
2. Recheck toggle bit because it may stop toggling as Q5 changes to "1".

AC CHARACTERISTICS

WORD/BYTE CONFIGURATION (BYTE#)

| Parameter | Description | | Speed Options | Unit |
|------------|-------------------------------|-----|---------------|------|
| | | | 70 | |
| Telf/Telfh | CE# to BYTE# from L/H | MAX | 5 | ns |
| Tflqz | BYTE# from L to Output Hiz | MAX | 25 | ns |
| Tfhqv | BYTE# from H to Output Active | MIN | 70 | ns |

Figure 23. BYTE# TIMING WAVEFORM FOR READ OPERATIONS (BYTE# switching from byte mode to word mode)



RECOMMENDED OPERATING CONDITIONS

At Device Power-Up

AC timing illustrated in Figure A is recommended for the supply voltages and the control signals at device power-up. If the timing in the figure is ignored, the device may not operate correctly.

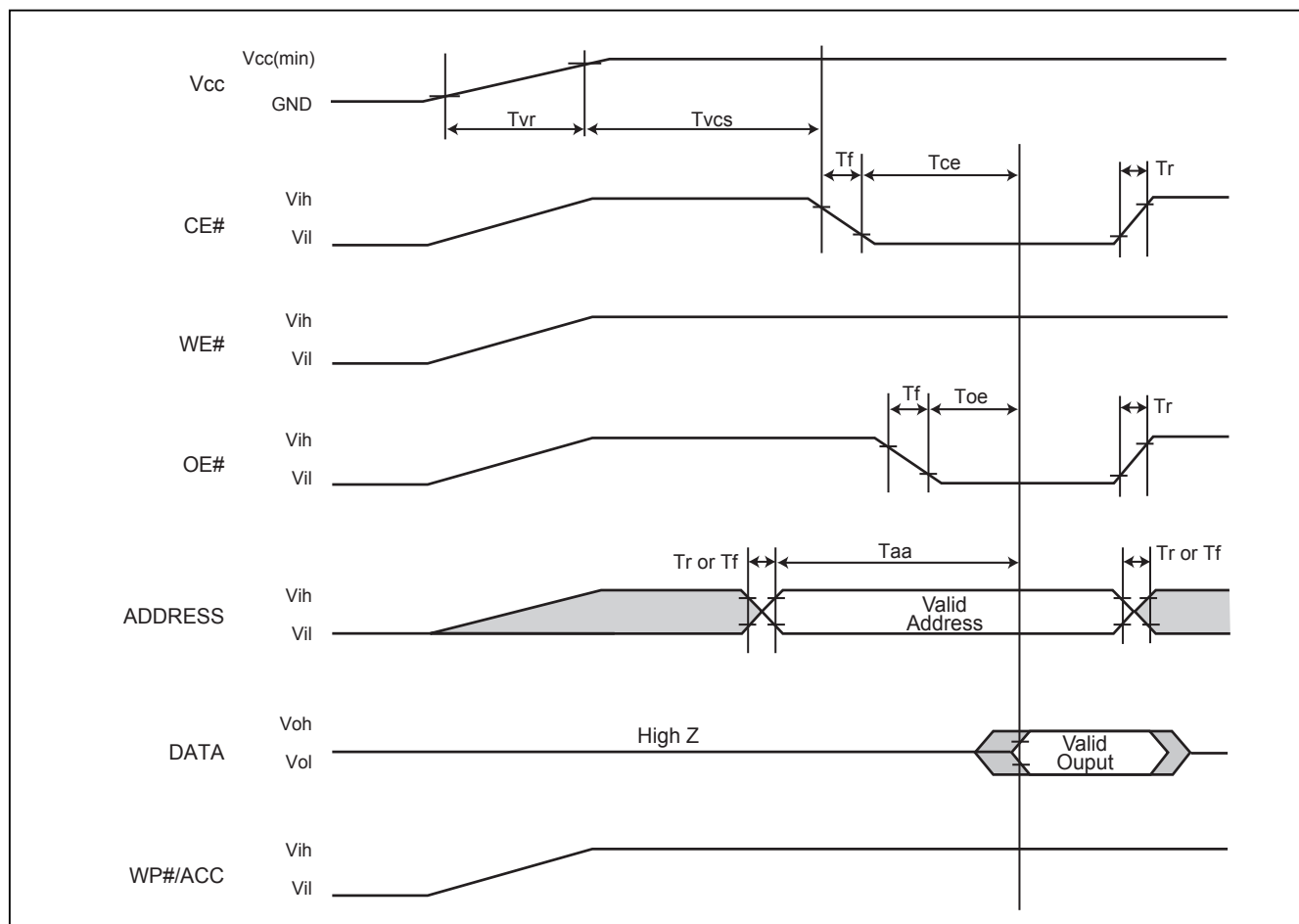


Figure A. AC Timing at Device Power-Up

| Symbol | Parameter | Min. | Max. | Unit |
|--------|------------------------|------|--------|------|
| Tvr | Vcc Rise Time | 20 | 500000 | us/V |
| Tr | Input Signal Rise Time | | 20 | us/V |
| Tf | Input Signal Fall Time | | 20 | us/V |
| Tvcs | Vcc Setup Time | 200 | | us |

ERASE AND PROGRAMMING PERFORMANCE

| PARAMETER | LIMITS | | | UNITS |
|------------------------------------|-----------|---------|------|--------|
| | MIN. | TYP. | MAX. | |
| Chip Erase Time | | 35 | 50 | sec |
| Sector Erase Time | | 0.7 | 2 | sec |
| Erase/Program Cycles | | 100,000 | | Cycles |
| Chip Programming Time | Byte Mode | 36 | 108 | sec |
| | Word Mode | 24 | 72 | sec |
| Accelerated Byte/Word Program Time | | 7 | 210 | us |
| Word Program Time | | 11 | 360 | us |
| Byte Programming Time | | 9 | 300 | us |

Notes:

1. Typical program and erase times assume the following conditions: 25°C, 3.0V VCC. Programming specifications assume checkboard data pattern.
2. Maximum values are measured at VCC = 3.0 V, worst case temperature. Maximum values are valid up to and including 100,000 program/erase cycles.
3. Erase/Program cycles comply with JEDEC JESD-47 & 22-A117 standard.

DATA RETENTION

| PARAMETER | Condition | Min. | Max. | UNIT |
|----------------|-----------|------|------|-------|
| Data retention | 55°C | 20 | | years |

LATCH-UP CHARACTERISTICS

| | MIN. | MAX. |
|---|--------|-----------|
| Input voltage difference with GND on all pins except I/O pins | -1.0V | 10.5V |
| Input voltage difference with GND on all I/O pins | -1.0V | 1.5 x Vcc |
| Vcc Current | -100mA | +100mA |

All pins included except Vcc. Test conditions: Vcc = 3.0V, one pin per testing

TSOP PIN CAPACITANCE

| Parameter Symbol | Parameter Description | Test Set | TYP | MAX | UNIT |
|------------------|-------------------------|----------|-----|-----|------|
| CIN2 | Control Pin Capacitance | VIN=0 | 7.5 | 9 | pF |
| COUT | Output Capacitance | VOUT=0 | 8.5 | 12 | pF |
| CIN | Input Capacitance | VIN=0 | 6 | 7.5 | pF |

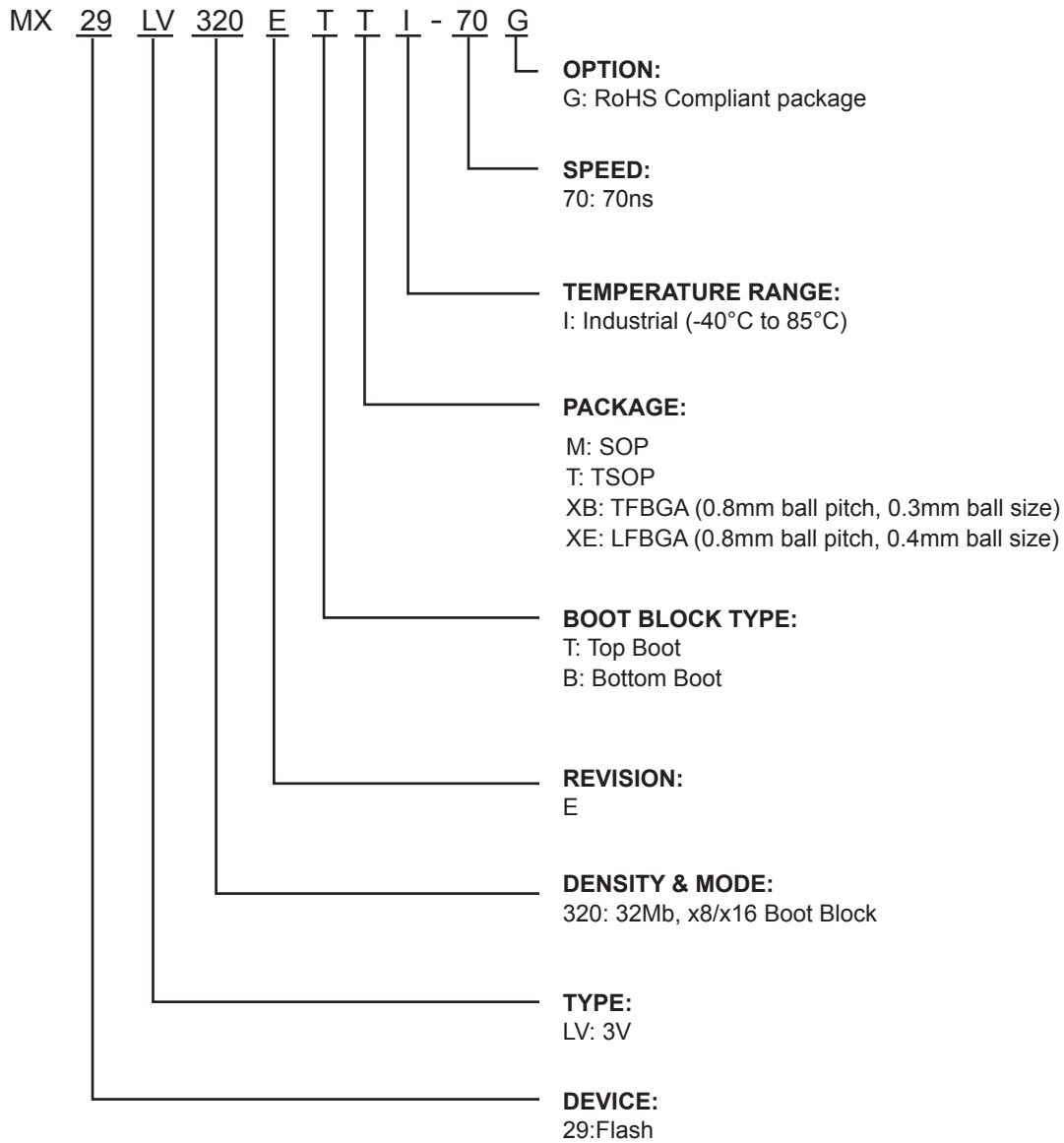


ORDERING INFORMATION

| PART NO. | ACCESS TIME (ns) | Ball Pitch/ Ball Size | PACKAGE | Remark |
|---------------------|-----------------------------|----------------------------------|----------------|----------------|
| MX29LV320ETMI-70G * | 70 | - | 44 Pin SOP | RoHS Compliant |
| MX29LV320ETTI-70G | 70 | - | 48 Pin TSOP | RoHS Compliant |
| MX29LV320EBTI-70G | 70 | - | 48 Pin TSOP | RoHS Compliant |
| MX29LV320ETXBI-70G | 70 | 0.8mm/0.3mm | 48-Ball TFBGA | RoHS Compliant |
| MX29LV320EBXBI-70G | 70 | 0.8mm/0.3mm | 48-Ball TFBGA | RoHS Compliant |
| MX29LV320ETXEI-70G | 70 | 0.8mm/0.4mm | 48-Ball LFBGA | RoHS Compliant |
| MX29LV320EBXEI-70G | 70 | 0.8mm/0.4mm | 48-Ball LFBGA | RoHS Compliant |

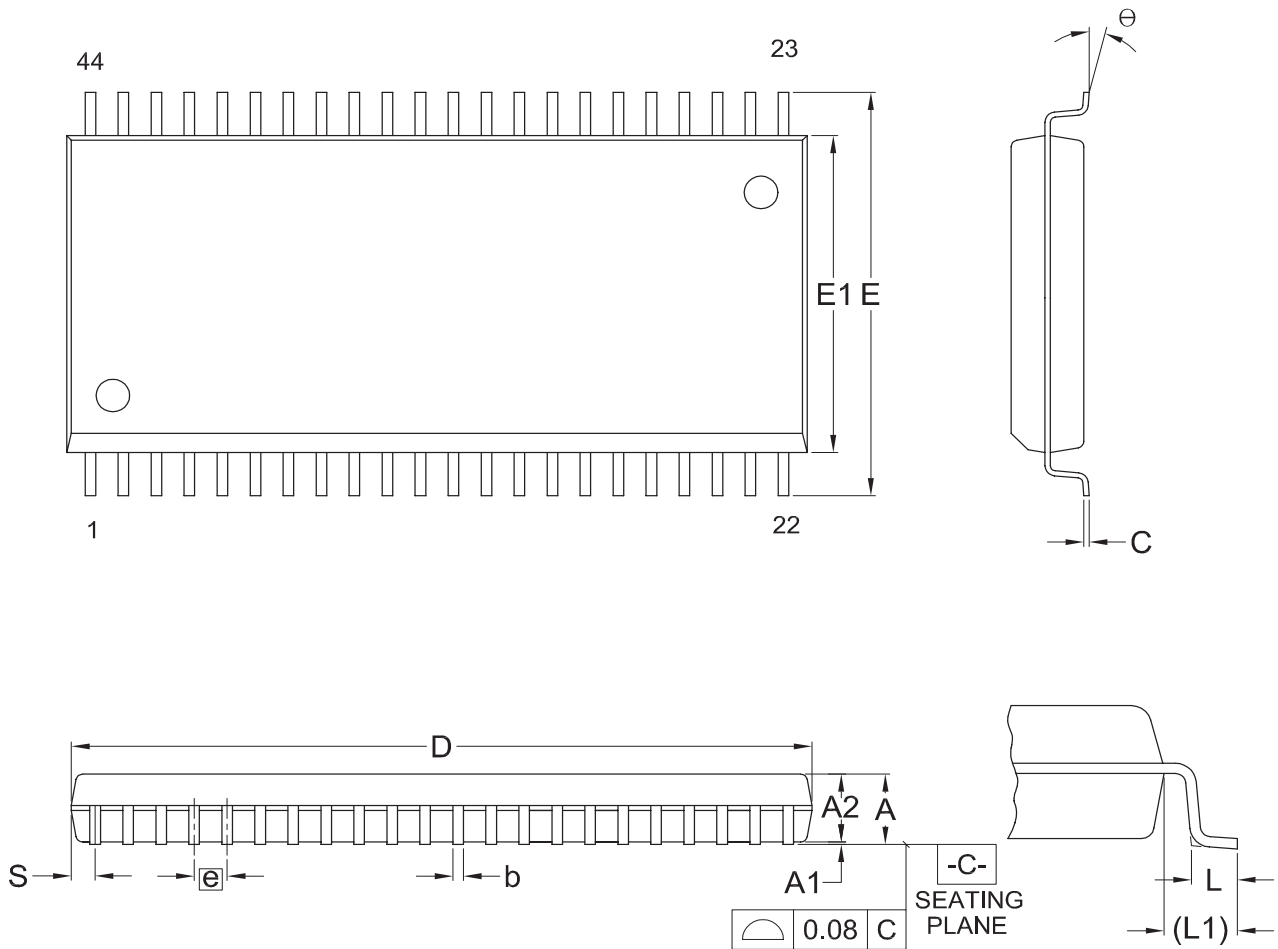
* 44-pin SOP is only for Pachinko Socket (Advanced Information).

PART NAME DESCRIPTION



PACKAGE INFORMATION

Doc. Title: Package Outline for SOP 44L (500MIL)

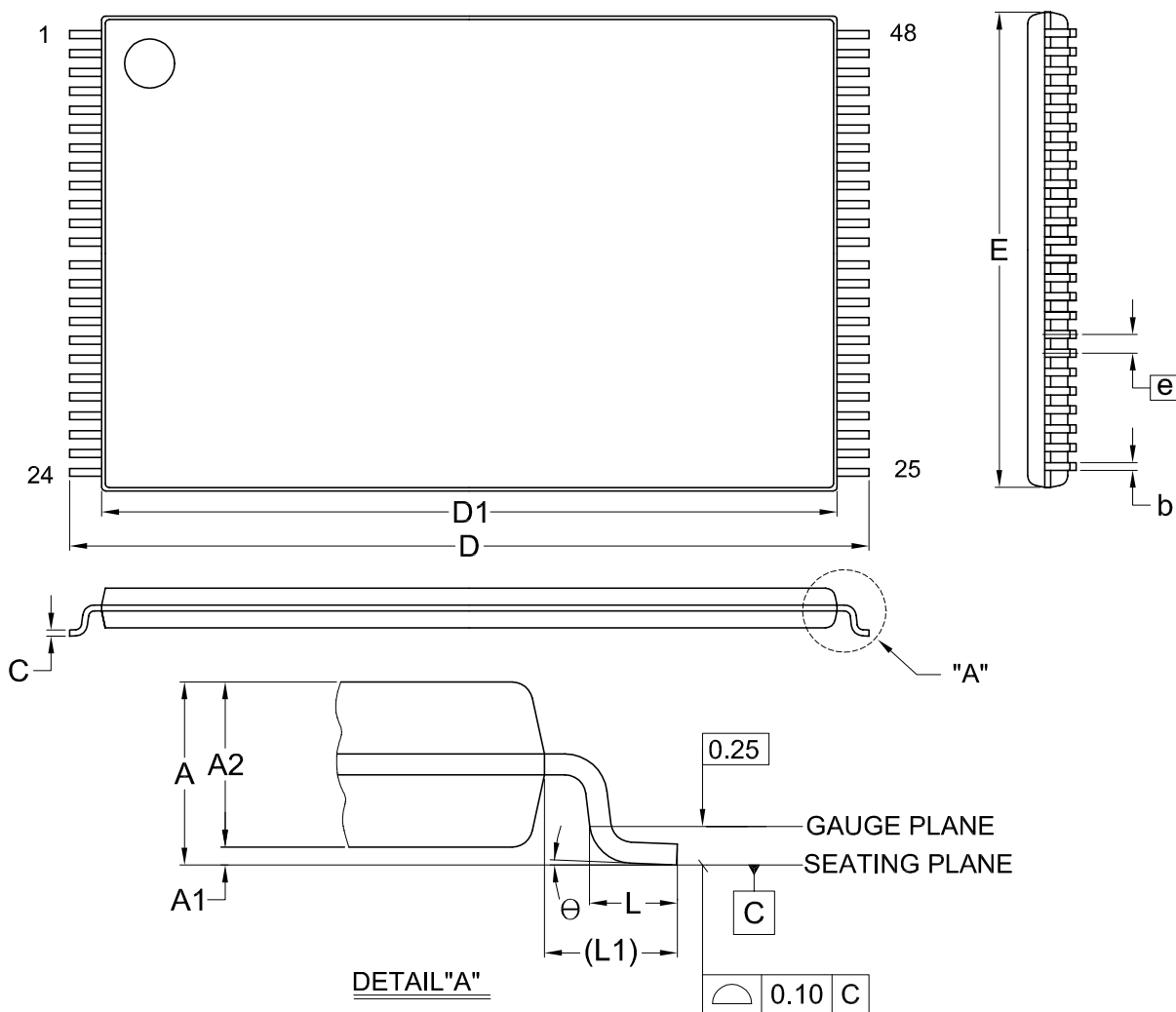


Dimensions (inch dimensions are derived from the original mm dimensions)

| SYMBOL | | A | A1 | A2 | b | C | D | E | E1 | e | L | L1 | S | θ |
|--------|------|-------|-------|-------|-------|-------|-------|-------|-------|-------|-------|-------|-------|----|
| UNIT | | | | | | | | | | | | | | |
| mm | Min. | --- | 0.10 | 2.59 | 0.36 | 0.15 | 28.37 | 15.83 | 12.47 | -- | 0.56 | 1.51 | 0.78 | 0 |
| | Nom. | -- | 0.15 | 2.69 | 0.41 | 0.20 | 28.50 | 16.03 | 12.60 | 1.27 | 0.76 | 1.71 | 0.91 | 5 |
| | Max. | 3.00 | 0.20 | 2.80 | 0.51 | 0.25 | 28.63 | 16.23 | 12.73 | -- | 0.96 | 1.91 | 1.04 | 10 |
| Inch | Min. | -- | 0.004 | 0.102 | 0.014 | 0.006 | 1.117 | 0.623 | 0.491 | --- | 0.022 | 0.059 | 0.031 | 0 |
| | Nom. | --- | 0.006 | 0.106 | 0.016 | 0.008 | 1.122 | 0.631 | 0.496 | 0.050 | 0.030 | 0.067 | 0.036 | 5 |
| | Max. | 0.118 | 0.008 | 0.110 | 0.020 | 0.010 | 1.127 | 0.639 | 0.501 | --- | 0.038 | 0.075 | 0.041 | 10 |

| DWG.NO. | REVISION | REFERENCE | | | ISSUE DATE |
|-----------|----------|-----------|------|--|------------|
| | | JEDEC | EIAJ | | |
| 6110-1405 | 7 | MO-175 | | | 2008/02/18 |

Title: Package Outline for TSOP(I) 48L (12X20mm)NORMAL FORM



Dimensions (inch dimensions are derived from the original mm dimensions)

| SYMBOL | | A | A1 | A2 | b | C | D | D1 | E | e | L | L1 | θ |
|--------|------|-------|-------|-------|-------|-------|-------|-------|-------|-------|-------|-------|---|
| UNIT | | | | | | | | | | | | | |
| mm | Min. | --- | 0.05 | 0.95 | 0.17 | 0.10 | 19.80 | 18.30 | 11.90 | — | 0.50 | 0.70 | 0 |
| | Nom. | --- | 0.10 | 1.00 | 0.20 | 0.13 | 20.00 | 18.40 | 12.00 | 0.50 | 0.60 | 0.80 | 5 |
| | Max. | 1.20 | 0.15 | 1.05 | 0.27 | 0.21 | 20.20 | 18.50 | 12.10 | — | 0.70 | 0.90 | 8 |
| Inch | Min. | --- | 0.002 | 0.037 | 0.007 | 0.004 | 0.780 | 0.720 | 0.469 | — | 0.020 | 0.028 | 0 |
| | Nom. | --- | 0.004 | 0.039 | 0.008 | 0.005 | 0.787 | 0.724 | 0.472 | 0.020 | 0.024 | 0.031 | 5 |
| | Max. | 0.047 | 0.006 | 0.041 | 0.011 | 0.008 | 0.795 | 0.728 | 0.476 | — | 0.028 | 0.035 | 8 |

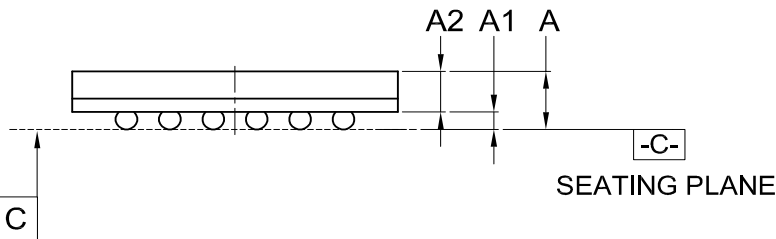
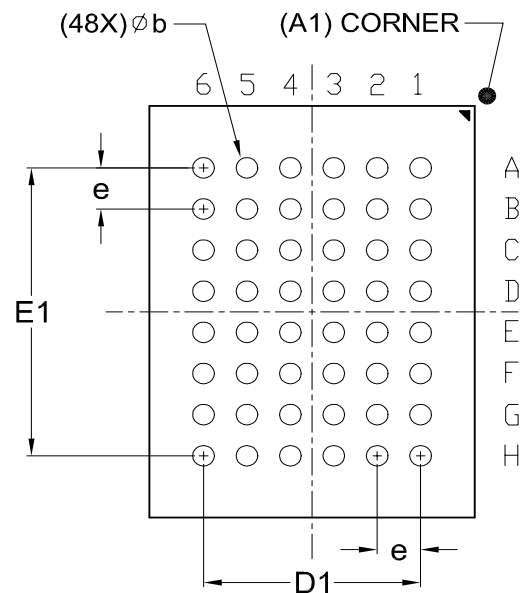
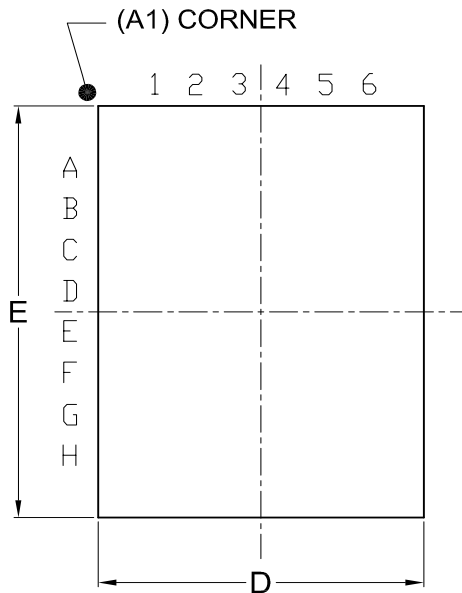
| DWG.NO. | REVISION | REFERENCE | | | ISSUE DATE |
|-----------|----------|-----------|------|--|------------|
| | | JEDEC | EIAJ | | |
| 6110-1607 | 8 | MO-142 | | | 2007/08/03 |

48-Ball TFBGA (for MX29LV320E TXBI/BXBI)

Title: Package Outline for CSP 48BALL(6X8X1.2MM,BALL PITCH 0.8MM,BALL DIAMETER 0.3MM)

TOP VIEW

BOTTOM VIEW



Dimensions (inch dimensions are derived from the original mm dimensions)

| SYMBOL | | A | A1 | A2 | b | D | D1 | E | E1 | e |
|--------|----|------|-------|-------|-------|-------|-------|-------|-------|-------|
| UNIT | mm | Min. | 0.18 | 0.65 | 0.25 | 5.90 | | 7.90 | | |
| | | Nom. | 0.23 | — | 0.30 | 6.00 | 4.00 | 8.00 | 5.60 | 0.80 |
| | | Max. | 1.20 | 0.28 | — | 0.35 | 6.10 | | 8.10 | |
| Inch | | Min. | 0.007 | 0.026 | 0.010 | 0.232 | | 0.311 | | |
| | | Nom. | 0.009 | --- | 0.012 | 0.236 | 0.157 | 0.315 | 0.220 | 0.031 |
| | | Max. | 0.047 | 0.011 | --- | 0.014 | 0.240 | | 0.319 | |

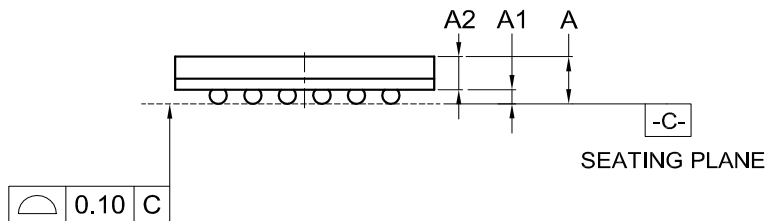
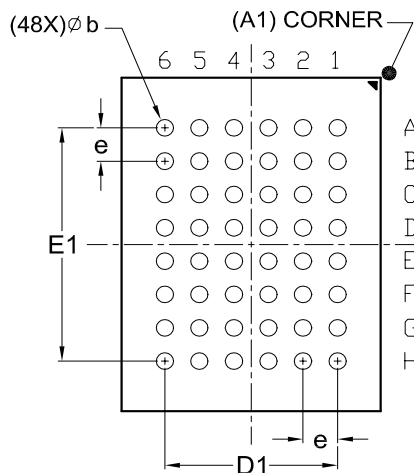
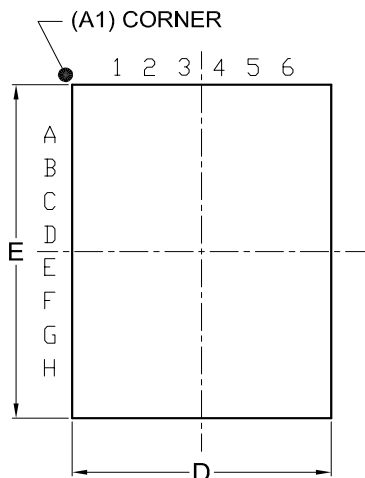
| DWG.NO. | REVISION | REFERENCE | | | ISSUE DATE |
|-----------|----------|-----------|------|--|------------|
| | | JEDEC | EIAJ | | |
| 6110-4201 | 6 | MO-210 | | | 03-29-'06 |

48-Ball LFBGA (for MX29LV320E TXEI/BXEI)

Title: Package Outline for CSP 48BALL(6X8X1.3MM,BALL PITCH 0.8MM,BALL DIAMETER 0.4MM)

TOP VIEW

BOTTOM VIEW



Dimensions (inch dimensions are derived from the original mm dimensions)

| SYMBOL | | A | A1 | A2 | b | D | D1 | E | E1 | e |
|--------|------|-------|-------|-------|-------|-------|-------|-------|-------|-------|
| UNIT | | | | | | | | | | |
| mm | Min. | --- | 0.25 | 0.65 | 0.35 | 5.90 | | 7.90 | | |
| | Nom. | --- | 0.30 | --- | 0.40 | 6.00 | 4.00 | 8.00 | 5.60 | 0.80 |
| | Max. | 1.30 | 0.35 | --- | 0.45 | 6.10 | | 8.10 | | |
| Inch | Min. | — | 0.010 | 0.026 | 0.014 | 0.232 | | 0.311 | | |
| | Nom. | — | 0.012 | — | 0.016 | 0.236 | 0.157 | 0.315 | 0.220 | 0.031 |
| | Max. | 0.051 | 0.014 | — | 0.018 | 0.240 | | 0.319 | | |

| DWG.NO. | REVISION | REFERENCE | | | ISSUE DATE |
|-----------|----------|-----------|------|--|------------|
| | | JEDEC | EIAJ | | |
| 6110-4202 | 4 | MO-219 | | | 12-12-'03 |



REVISION HISTORY

| Revision No. | Description | Page | Date |
|---------------------|---|---------------------------|-------------|
| 1.0 | 1. Removed "Advanced Information" 2. Revised Table 4-4. CFI Mode: Primary Vendor-Specific Extended Query Data Values 3. Revised ORDERING INFORMATION | P5 P32 P61 | MAY/27/2010 |
| 1.1 | 1. Revised General Description-security sector size 2. Revised ORDERING INFORMATION | P6 P61 | JUN/14/2010 |
| 1.2 | 1. Added Top/Bottom Boot Security Sector Addresses tables 2. Modified Security Sector Flash Memory Region description 3. Modified description for RoHS compliance | P12,14 P27 P6,61,62 | MAY/23/2011 |



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MX29LV320E T/B

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